

Recent advances in CMOS pixel sensors: towards more applications

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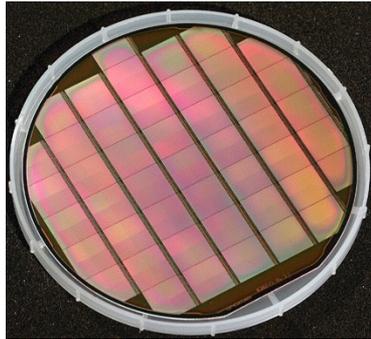


- Basics of CMOS pixels
- Projects in HEP: sensors & systems
- Tracking at low energy
- Non-tracking projects

Basic of CMOS pixel sensors

- *The technology*
- *Signal & Noise*
- *Architectures*

Main features



■ Industrial technology

- Integrated circuits (chips)
 - Lithography feature size $\ll 1\mu\text{m}$
 - Reticule limits $\approx 25 \times 30\text{ mm}^2$
- } constantly improving

■ Main features

- Small pixel size possible down to few μm^2
- Signal processing on chip
 - In-pixel amplification \rightarrow high SNR: “active”
 - No additional FEE readout: “monolithic”

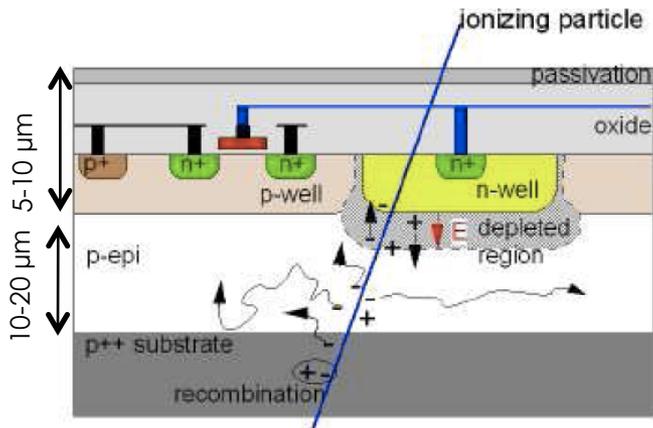
• Sensitive layer

- Thin
 - Resistivity (10 to $10^3\ \Omega \cdot \text{cm}$)
 - \rightarrow drives charge collection
- } possibly adapted to radiation type

- Operation at room temperature

■ Invention of CMOS sensors for light

- Early works late 60's
- 1993 paper by E.Fossum



Useful thickness: 30 μm

Speeding up the architecture

Tracking (4D-pattern recognition) works with very low occupancy
Basic idea = send less information

■ Definitions:

- **Full** read-out
= all pixel signals
sent out
 - **Sparse** read-out
= only pixel with
“high” signal
sent out
- need discrimination
(thresholding)



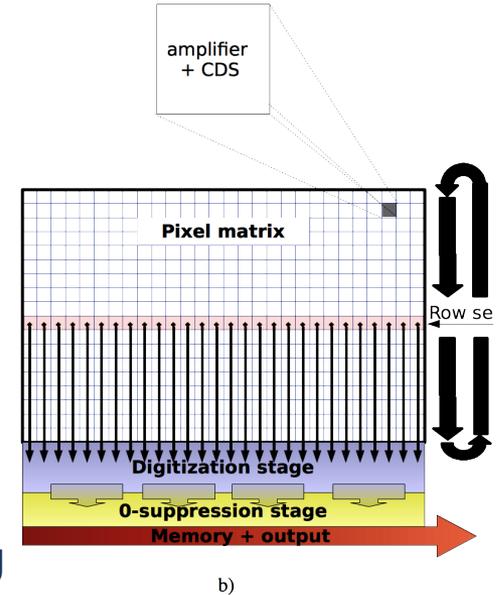
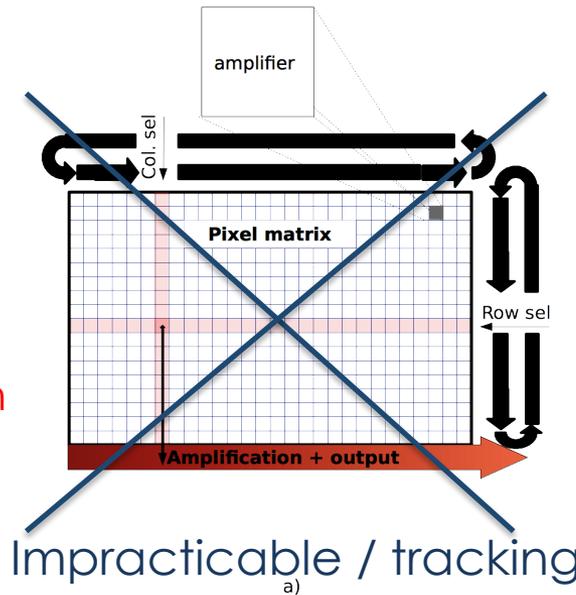
Average occupancy ~ maximum/10

Basic of read-out architectures

(obviously over-simplifying)

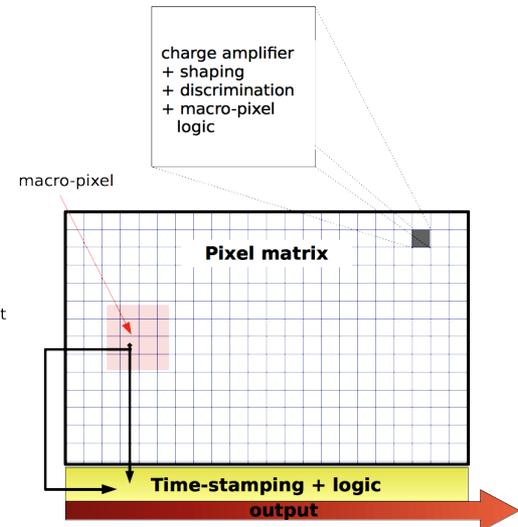
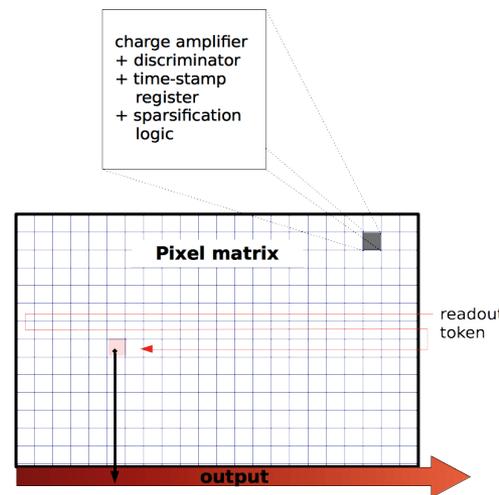
■ Synchronous

- Integration time = frame time
- Size efficient / pixel pitch



■ Asynchronous

- Integration time = amplifier properties
- Frame time = data stored * output speed
- Time-stamping friendly



Initial pros & cons

■ Full detection chain

sens. layer ➡ q-collect ➡ ampli ➡ analog treat ➡ A-D conv ➡ digital proc

sensor:  **+FEE** 

CIS: 

■ Obvious advantages

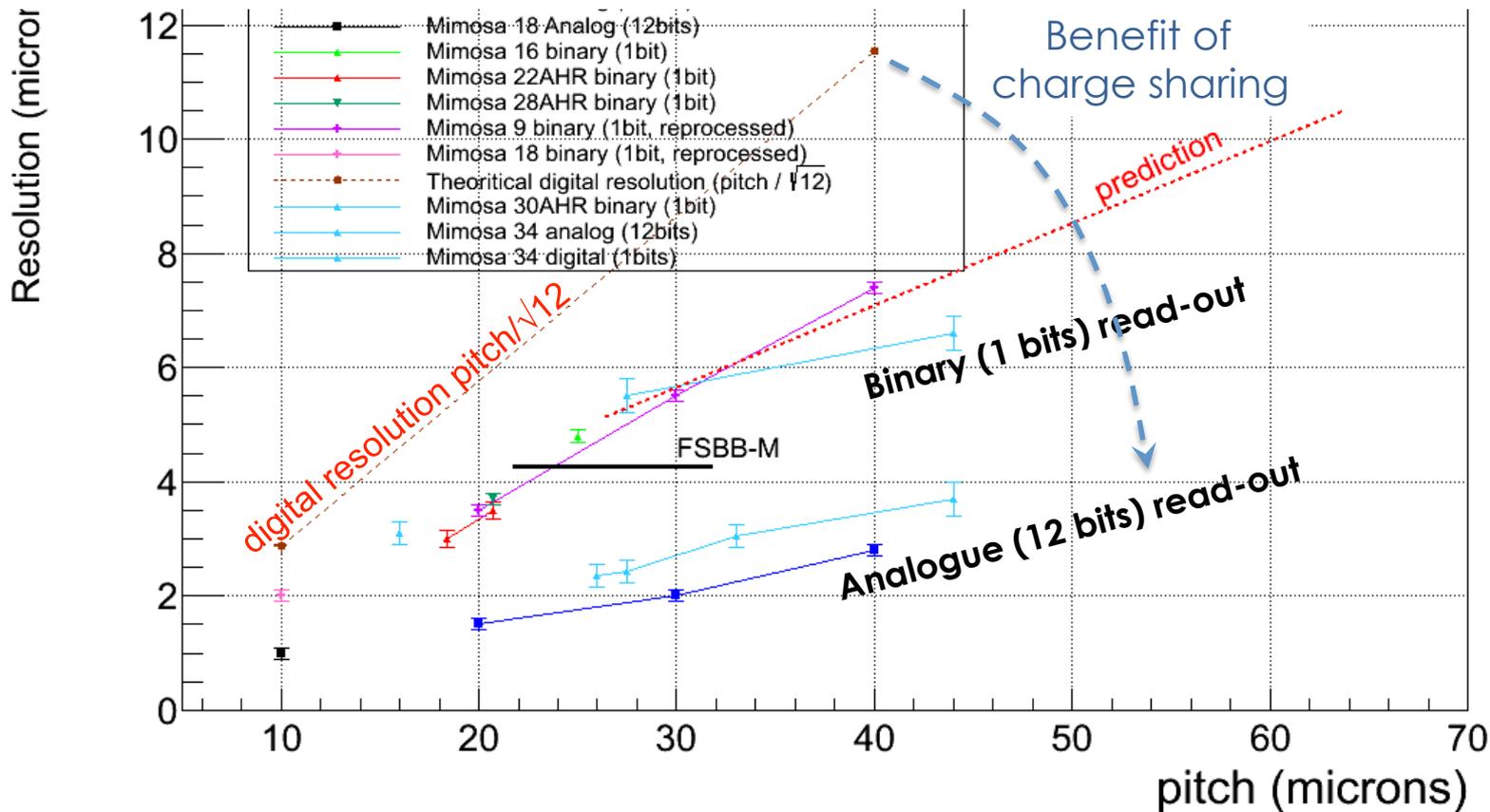
- Early ampli
 - high sensitivity
- Smartness
 - limit data throughput
- Complete system on a chip
 - easy to integrate
- Low fabrication cost

■ Some limitations

- Conflicting design parameters
 - ex: granularity vs speed
- 1 sensor = 1 system
 - no further optimization after fab.
- Development cost not small
- Same technology for all functions
 - Mitigated by 3D integration

Spatial resolution performances

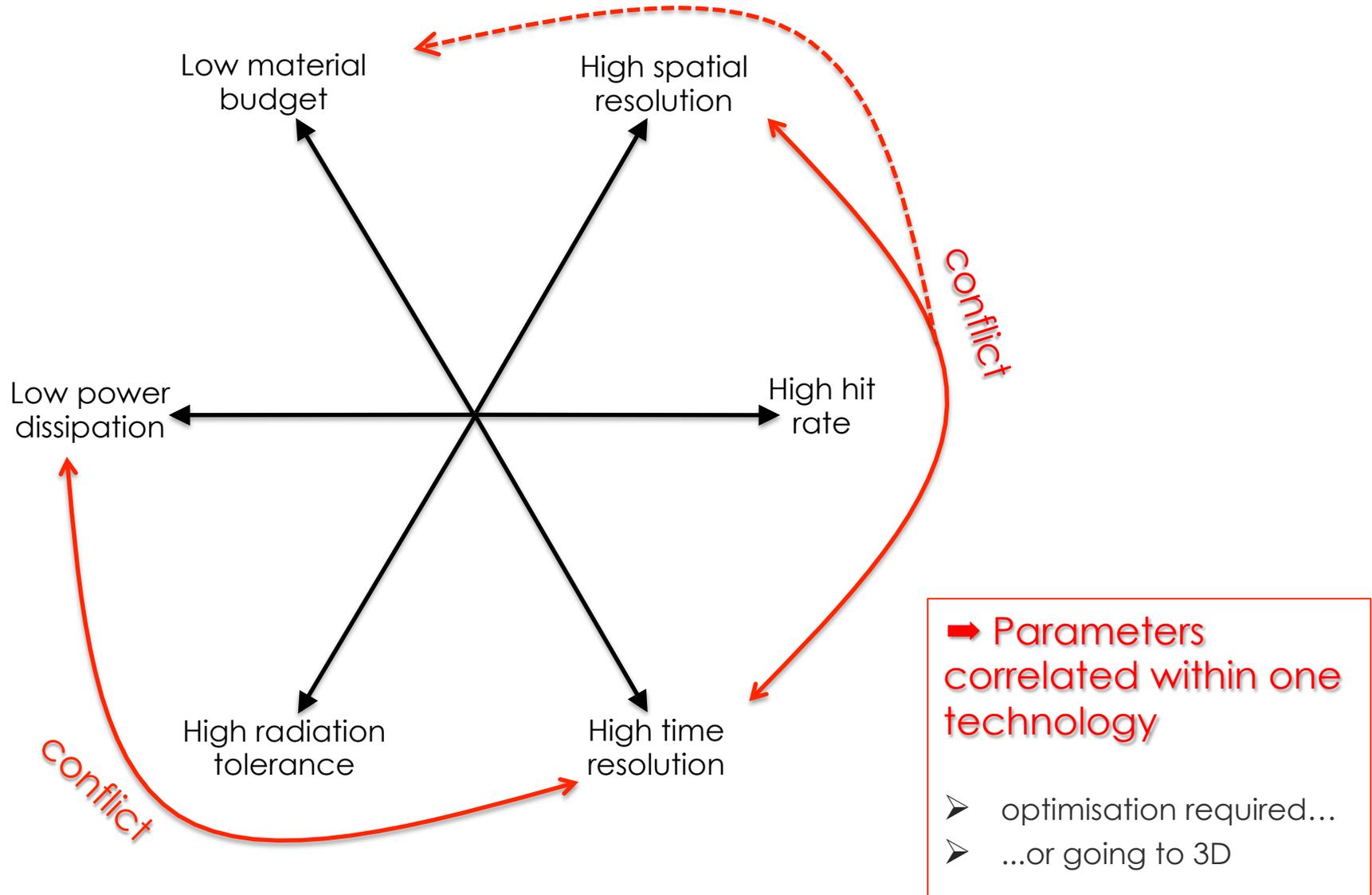
From many prototypes, the MIMOSA series from Strasbourg
(for thin non-depleted sensitive layers)



Tracking in High Energy Physics

	SLD	CMS LHC	STAR	CBM	ALICE	Belle-II	ILC	CLIC	ATLAS HL-LHC
Collision system	e ⁺ e ⁻	p+p	A+A p+p	A+A	A+A p+p	e ⁺ e ⁻	e ⁺ e ⁻	e ⁺ e ⁻	p+p
Spatial resolution (μm)	2	13	< 10	~5	~5	< 10	≤ 3	≤ 3	
Material Budget (% X0)	0.4	~2	~0.3	~0.3	~0.3	~0.2	≤ 0.2	≤ 0.3	<1
Hit rate (10⁶ s⁻¹cm⁻²)		O(20)	O(0,1)	O(1-10)	O(1)	100	O(0,2)	O(1)	O(200)
Time figure	0,2 s	25 ns	200 μs	~10 μs	<30 μs	~1 μs	O(10)μs	10 ns	25 ns
Radiotolerance (Mrad) (n_{eq}/cm²)	-	100 < 10¹⁵	O(0,2) O(10 ¹²)	O(30) < 10¹⁴	O(0.7) O(10 ¹³)	O(20) < 10 ¹³	O(0,1) < 10 ¹²	O(20) < 10 ¹⁴	500 <10 ¹⁷
Power dissipated (W/cm²)	-		0.1	1-2	~0.3	~2	0.1	0.1	

Requirements on sensing layers



Tracking in HEP: Sensors

→ *Heavy-ion collisions*

→ *p+p @ LHC*

→ *e⁺+e⁻ colliders*

STAR @ RHIC (2014)

- Material budget $\sim 0.4 \% X_0$
- Single point resolution $\sigma_{\text{point}} \lesssim 10 \mu\text{m}$
- Only vertexing

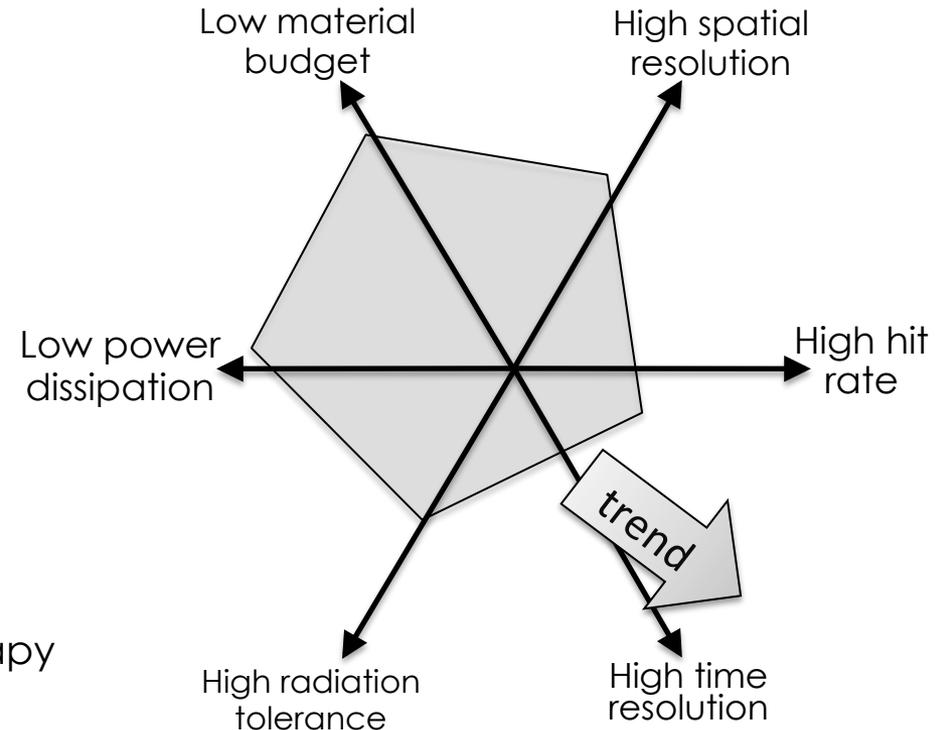
ALICE @ LHC (2021)

- Higher rate $\Rightarrow \sigma_{\text{time}} \sim 10 \mu\text{s}$
- Single point resolution $\sigma_{\text{point}} \lesssim 5 \mu\text{m}$
- Vertexing & **tracking** (newITS)
 - Large surface \rightarrow cost

Fixed target experiments

- Measurement of Xsections / hadrontherapy
- FIRST (GSI 2011-2012)
- FOOT (Italy, Germany, France)
 - \rightarrow See Eleuterio's talk

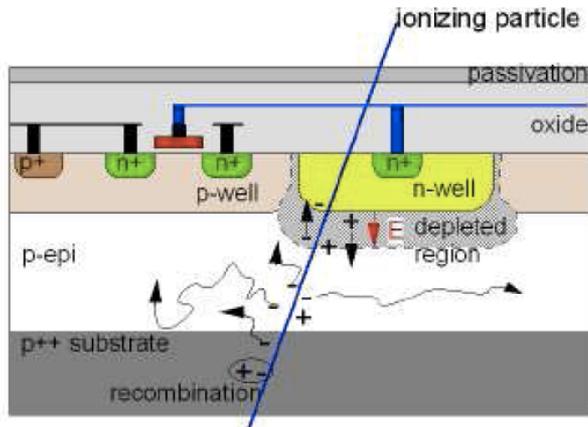
EIC (?)



Technical choice

- \Rightarrow hybrid (current ALICE-ITS)
- \Rightarrow monolithic

STAR – MIMOSA-28



- **Technology:**
AMS 0.35 μm
- **Sensitive layer:**
400 $\Omega \cdot \text{cm}$

Key elements

- In-pixel CDS \rightarrow discri possible
- Column // read-out
BUT one row at a time
- Synchronous digitization
 - discriminator (1bit)
- Synchronous zero-suppression
 - address pixels per group

Distinct features

- Read-out time = integration time
- Insensitive area aside the pixel matrix
- Counting rate \leftarrow size and speed zero-supp. stage

\rightarrow Counting rate: $> 10^6$ hits/cm²/s

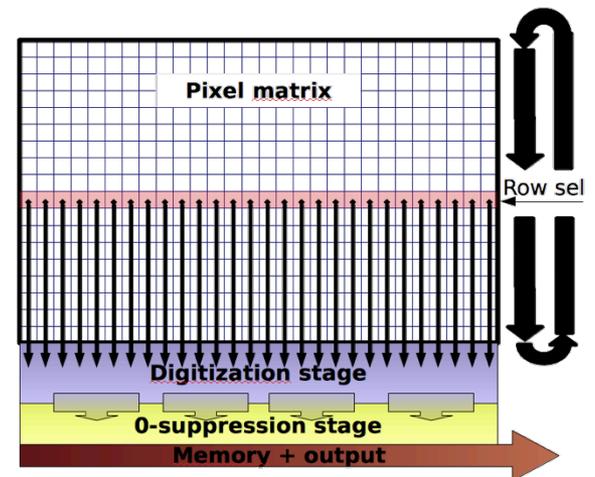
2008-2011

MIMOSA 28

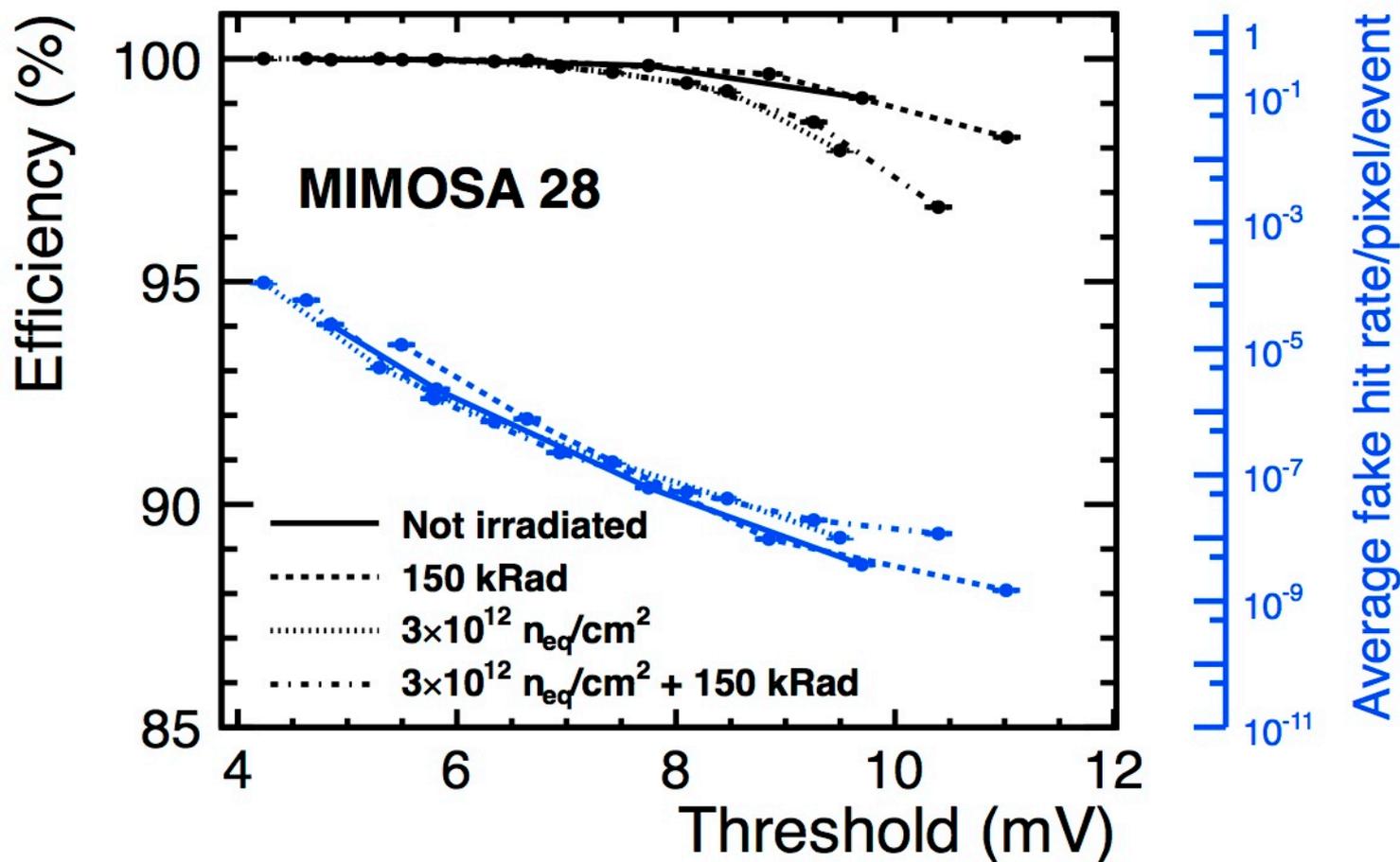
960x928 ~ 0.9 Mpixels
pitch 20.7x20.7 μm^2

- \rightarrow Sensitive area 19.7x19.2 mm²
- \rightarrow Total area 20.2x22.7 mm²
- \rightarrow readout time 200 μs

\rightarrow Power diss ~ 150 mW/cm²



MIMOSA-28 performances

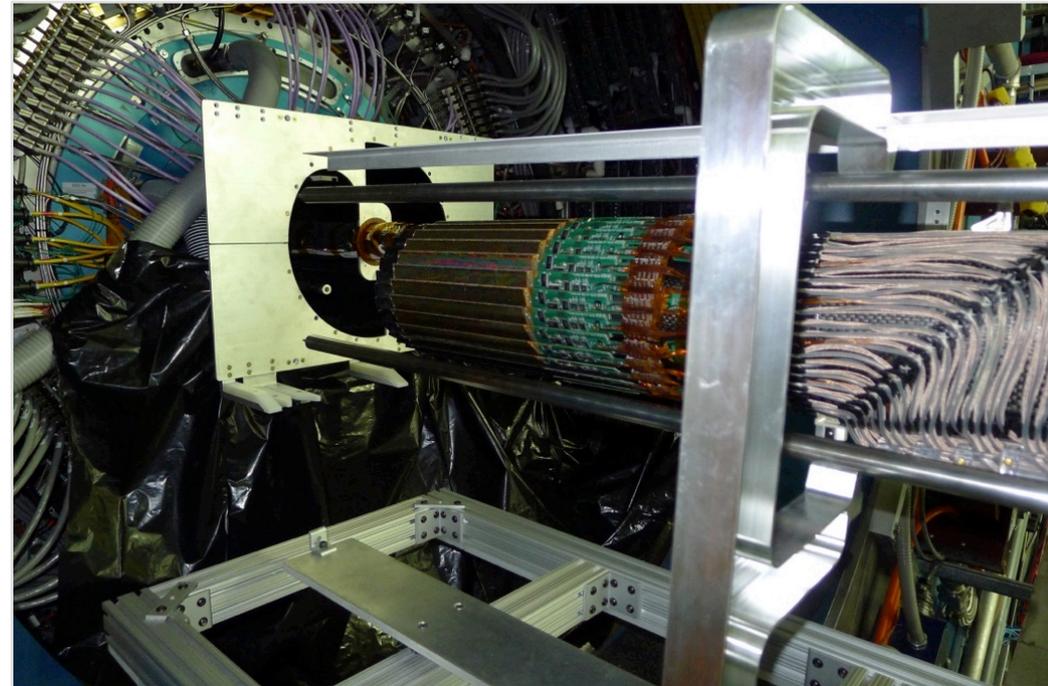


STAR-PXL = the first MAPS detector

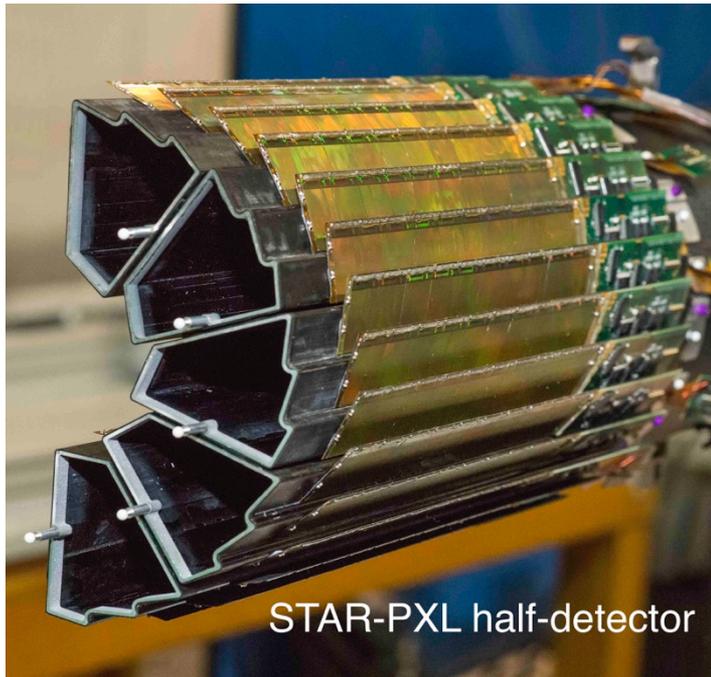
- 400 MIMOSA-28 sensors
- 360 10^6 pixels
- Air flow cooling $T_{op} \lesssim 35^\circ\text{C}$
- $\sigma_{s.p.} \approx 4 \mu\text{m}$
- mat. budget = 0.39 % X_0 / layer
- Read-out time $\sim 190 \mu\text{s}$

→ operated from 2014 to 2016

Detector developed by LBNL, U.Texas, CCNU



Cantilever support



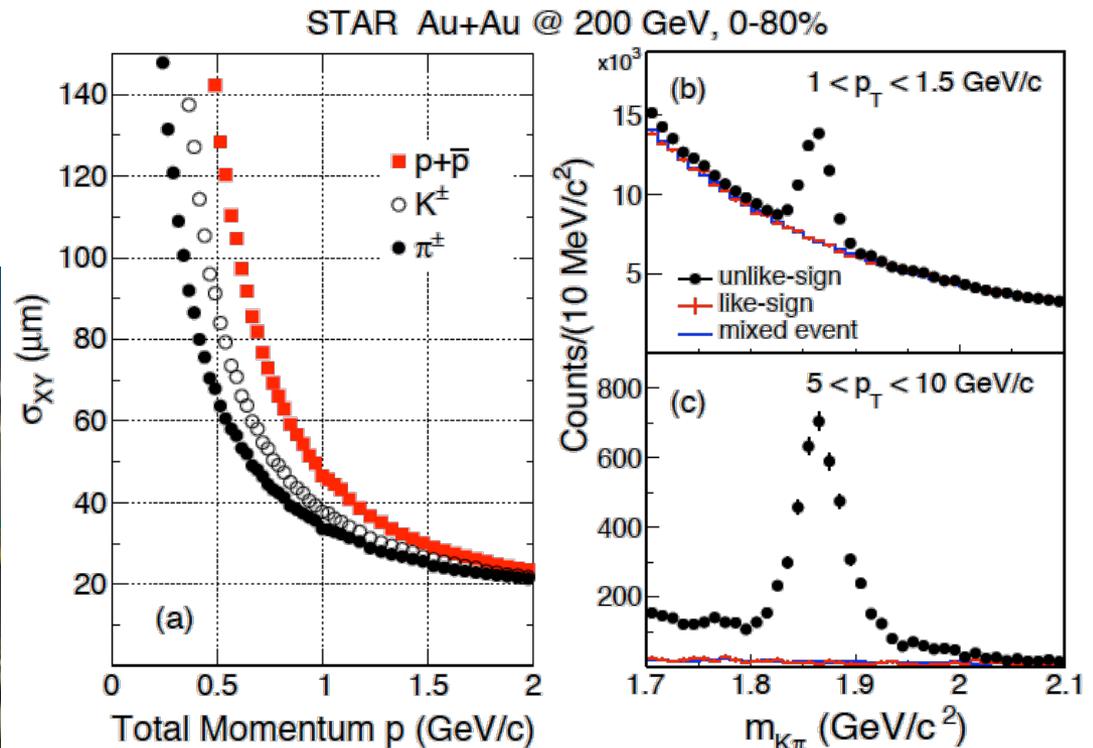
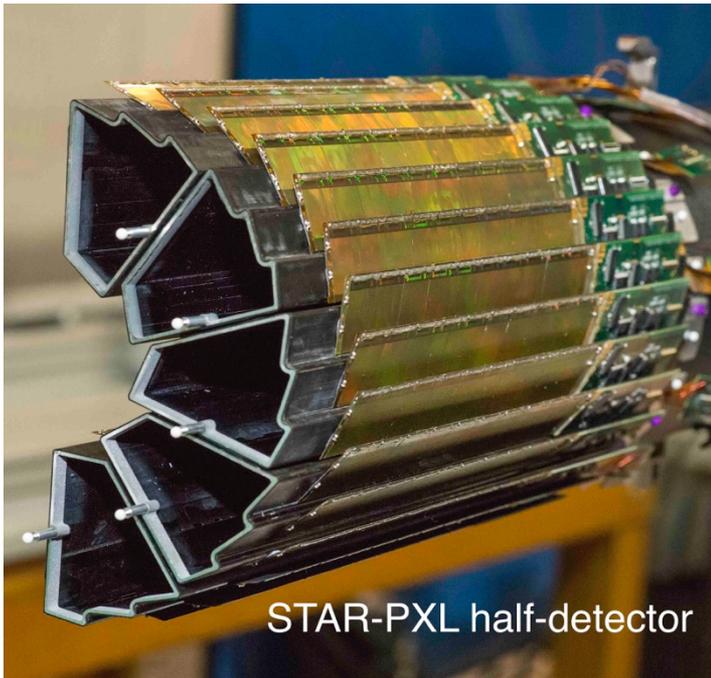
STAR-PXL half-detector

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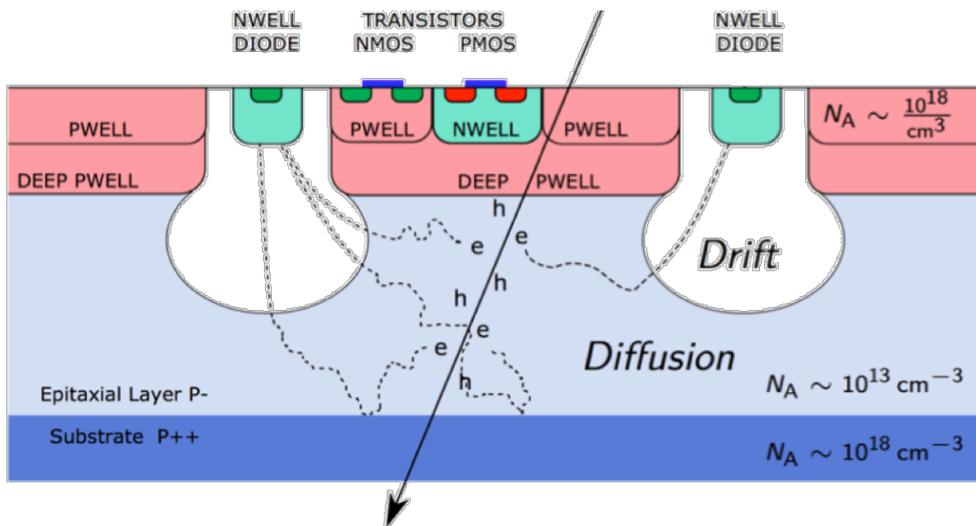
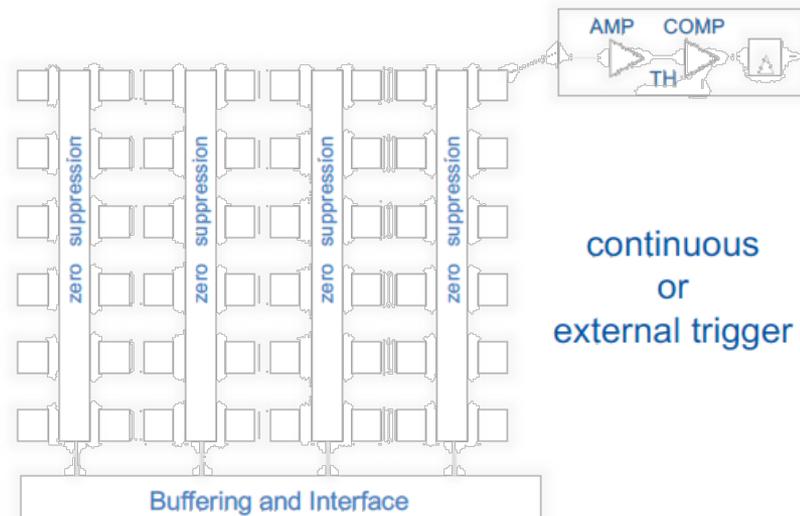
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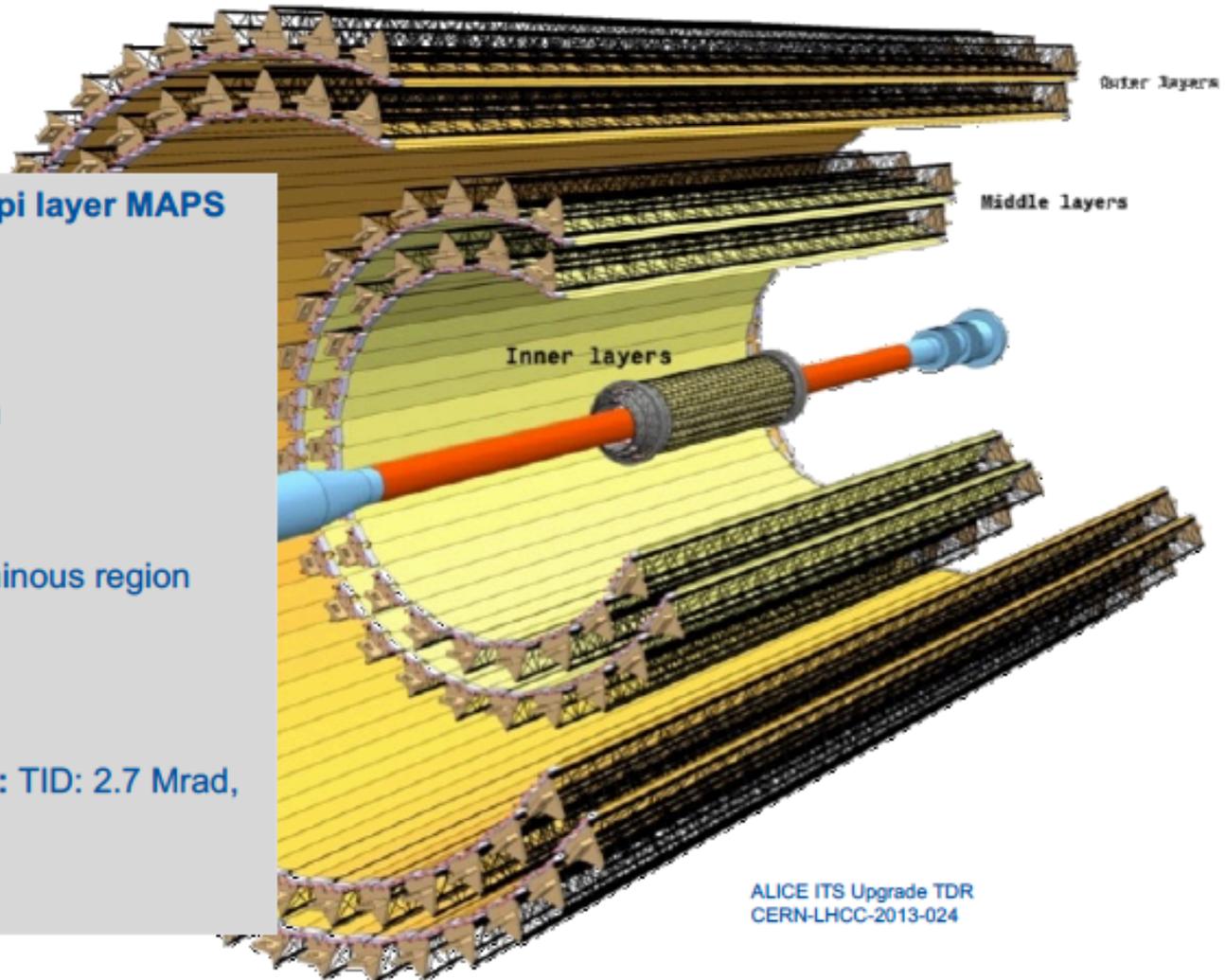


■ New technology, new architecture

- Developed @ CERN with many contributors
- Pixel size $29 \times 27 \mu\text{m}^2$
- $30 \times 15 \text{ mm}^2$
- Spatial resolution $5 \mu\text{m}$
- Integration time $\sim 5 \mu\text{s}$
- Power dissipation 40 mW/cm^2



- **Technology:**
TowerJazz $0.18 \mu\text{m}$
- **Sensitive layer:**
> $1 \text{ k}\Omega \cdot \text{cm}$
→ some depletion / back-bias



Based on high resistivity epi layer MAPS

- 3 Inner Barrel layers (IB)
- 4 Outer Barrel layers (OB)

Radial coverage: 21-400 mm

~ 10 m² 12.5 Gpixels

$|\eta| < 1.22$ over 90% of the luminous region

- 0.3% X_0 /layer (IB)
- 0.8 % X_0 /layer (OB)

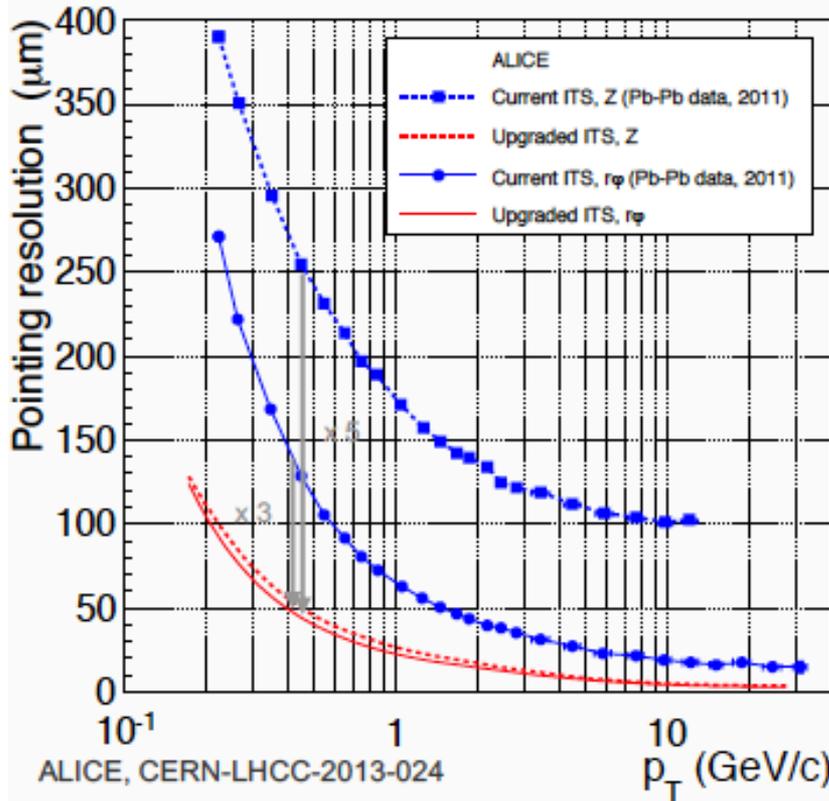
Radiation level (IB, layer 0): TID: 2.7 Mrad,
 1.7×10^{13} 1 MeV n_{eq} cm⁻²

Installation during LS2

ALICE ITS Upgrade TDR
CERN-LHCC-2013-024

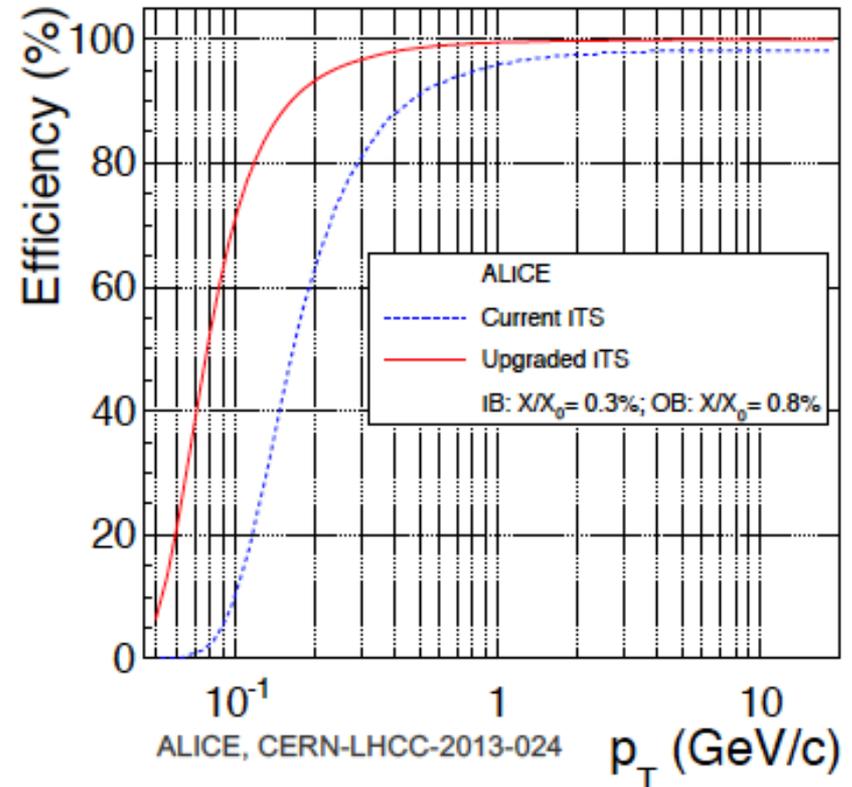
Expected tracking performances, from simulations

Impact parameter resolution



Improved impact parameter resolution

Track reconstruction efficiency



High standalone tracking efficiency

- **Objective: Sensor equipping Micro-Vertex Detector (MVD) of heavy-ion CBM expt at FAIR/GSI**

- 4 double-sided stations equipped with 50 μm thin CPS, operated in vacuum at $T_{op} \sim -40^\circ C$
- MIMOSIS sensor: asynchronous read-out architecture derived from ALPIDE sensor (ALICE-ITS)

- **Sensor target performances:**

- Spatial & Time resolutions $\lesssim 5 \mu m$ & $5 \mu s$
- Radiation tolerance $\gtrsim 3 \text{ MRad} \oplus 3 \cdot 10^{13} \text{ n}_{eq}/\text{cm}^2$
- Power: 200-350 mW/cm^2 (depending on distance to target)
- Hit/Data rate capability: $1.5\text{-}7 \cdot 10^5/\text{mm}^2/\text{s} \Rightarrow 1.6 \text{ Gbits}/\text{cm}^2/\text{s}$

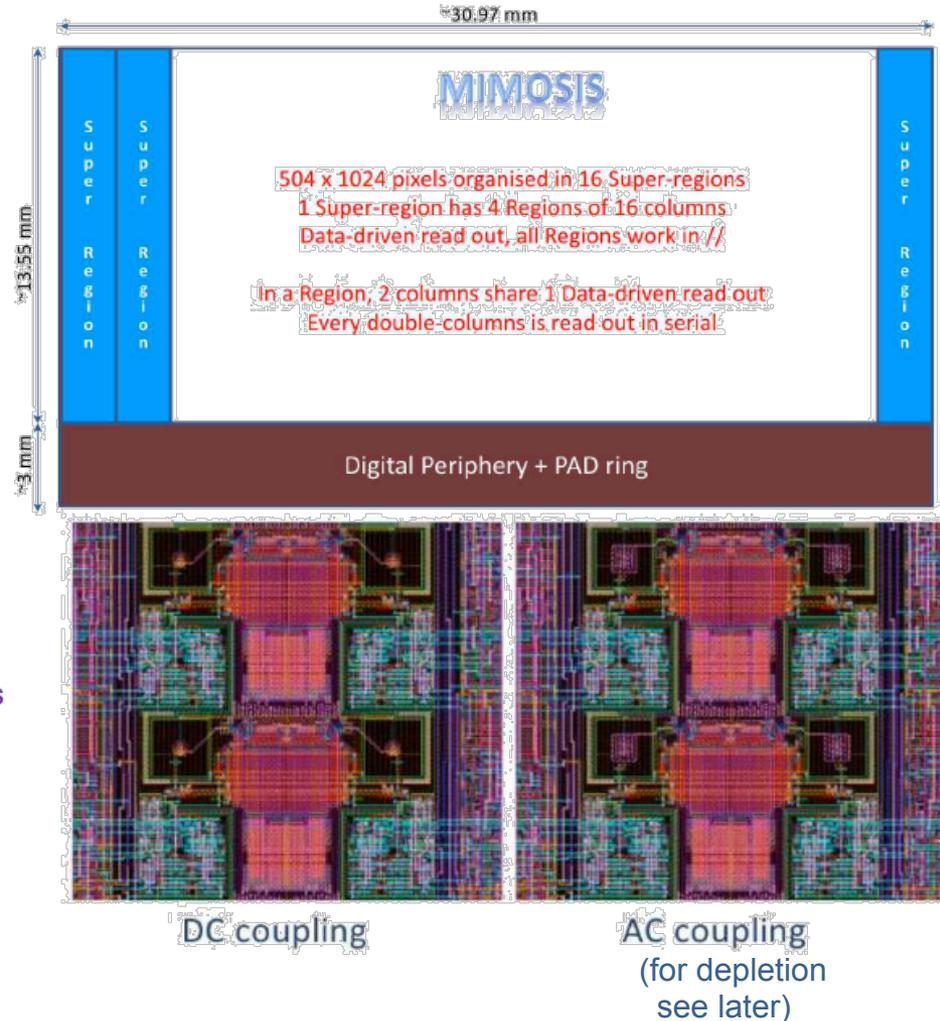
- **Technology:**

TowerJazz 0.18 μm

- **Sensitive layer:**

$> 1 \text{ k}\Omega \cdot \text{cm}$

- First small proto in 2017, engineering runs for 2018,19,**20**

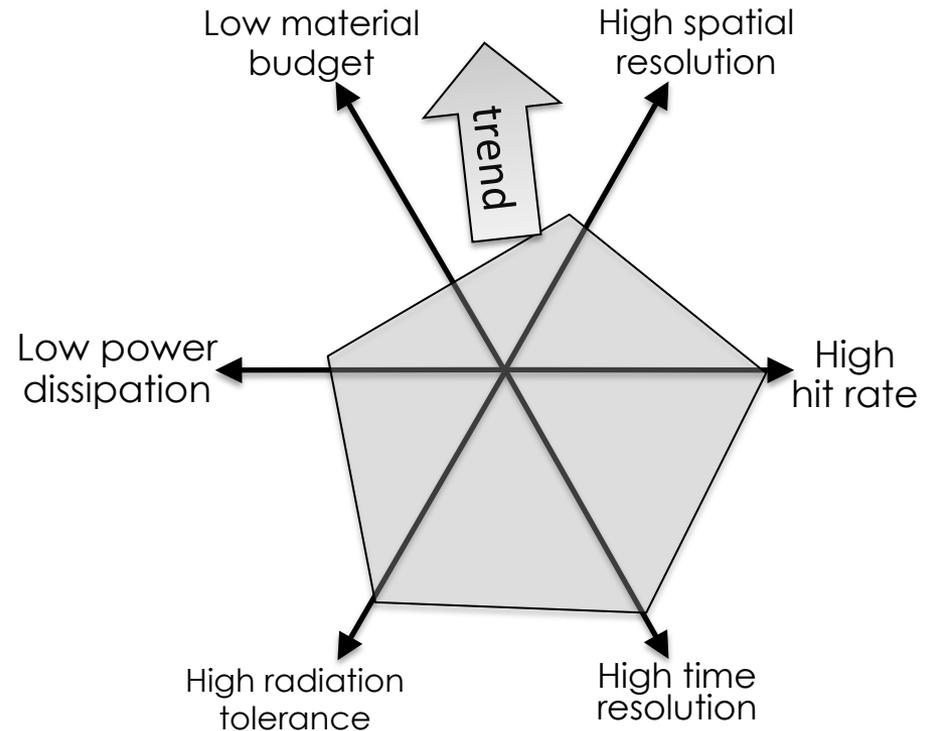


■ Current LHC (2008-21)

- Beam-crossing every **25 ns**
 - 40 collisions / beam crossing
 - Few 1000 tracks / event
- Radiation at 4-5 cm
 - 500 kGy / year
 - few $10^{14} n_{eq}(1 \text{ MeV})/\text{cm}^2$

■ High-luminosity LHC (>2024)

- Instantaneous lumi x10
 - Pile-up of 200-400 p+p collisions
- Radiation
 - **15 MGy / year**
 - few $10^{16} n_{eq}(1 \text{ MeV})/\text{cm}^2$
- Improved track param. resolution
 - material budget $\sim \% X_0$
 - Single point resolution $\sigma_{point} \sim 10 \mu\text{m}$



Technical choices

**\Rightarrow hybrid in inner layers
(\Rightarrow monolithic in outer layers)**

Intermezzo / sensing layer engineering



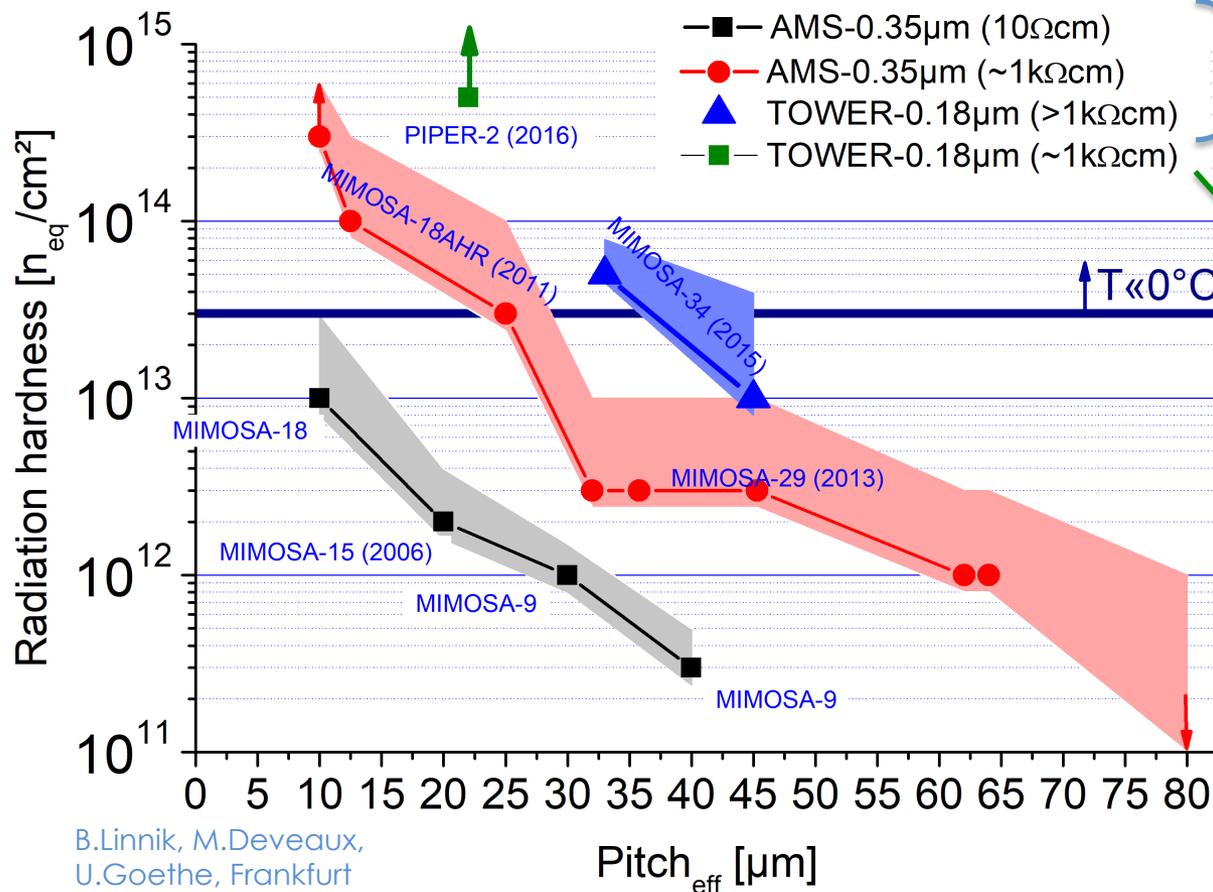
■ Impact of radiations

- Total Ionising Dose (TID)
 - Charges trapped at oxide/Si surfaces
 - Randomly released (I_{leak})
→ higher noise
 - Change transistor behaviours
 - Not sensor specific
- Highly ionising particle
 - Various Single Event Effects
 - Overcurrent, logic defaults...
 - Not sensor specific
- Non Ionising Energy Loss (NIEL)
 - Damage Si crystal
 - Trap charges → lower signal
 - Increases I_{leak} → higher noise

■ Potential cures

- Specific design rules
 - Not sensor specific
- Lower temperature
 - Mitigate leakage current (I_{leak})
- Focus charges on lower number of pixels
 - Increases signal
 - With denser collection nodes
⇐ smaller pixels
 - With drift field
⇐ depleted sens. volume

NIEL mitigation



undepleted sensors:
 Thermal diff. > drift
 collection time > 100 ns
 large charge sharing

depleted sensors
 mostly drift
 collection time few ns
 ~no charge sharing

B.Linnik, M.Deveaux,
 U.Goethe, Frankfurt

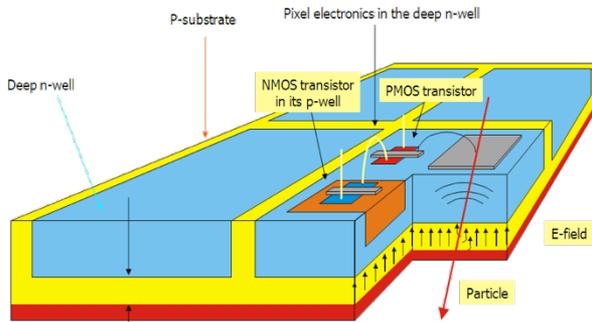
Similar impact for TID:

- Undepleted ~ 300 kRad
- Depleted ~ 1 GRad

Three ways to deplete MAPS

Depletion depth $\propto (V_{\text{bias}} \times \rho)^\alpha$ with $\alpha \leq 1/2$

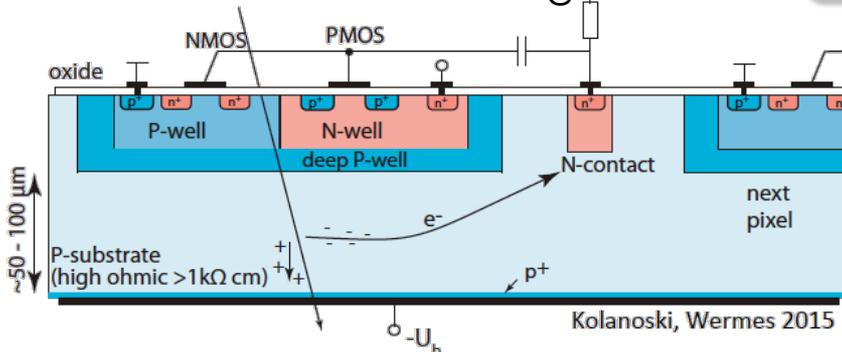
High Voltage



I.Pieric 2010

High Resistivity

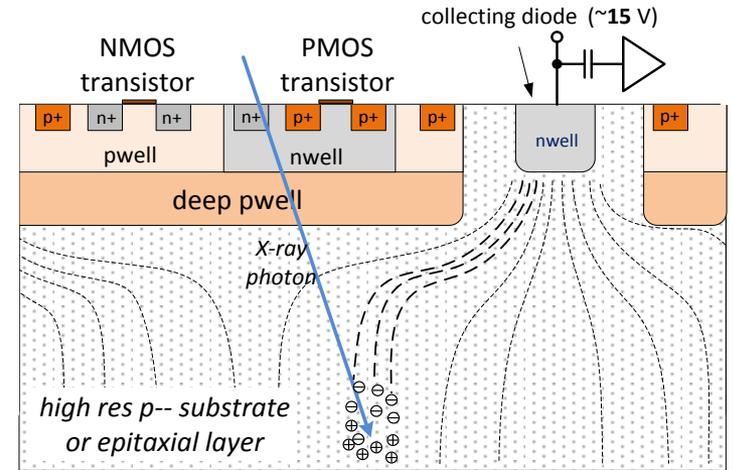
- Back biasing



Target fast timing

High Resistivity

- Top biasing



M.Kachel 2013

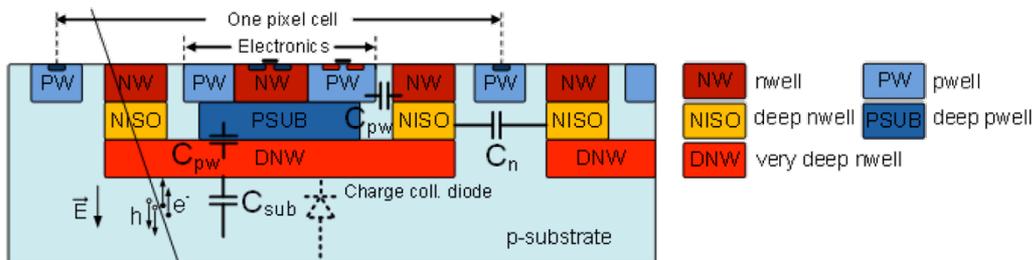
Target small pixels

* All with multiple wells
CMOS process:
Remember hybrid tech.
offers natural shielding

ATLAS – MAPS: full-depletion

■ Monopix

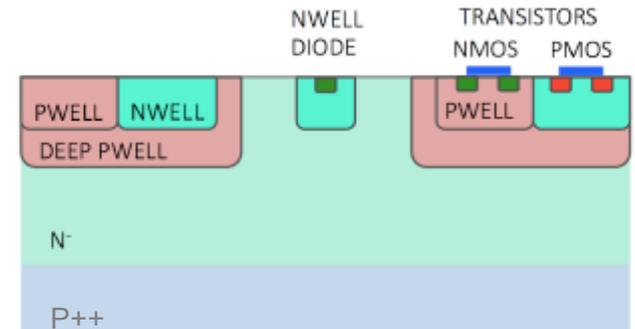
- L-Foundry 150 nm
 - High-res, $V_{bias} \sim 100-300$ V
- “large fill factor” diode
- Pixel size $250 \times 50 \mu\text{m}^2$
 - $36 \mu\text{W}/\text{pixel}$ for 25 ns read-out



U.Bonn, CPPM, IRFU

■ MALTA

- Tower Jazz 180 nm
- “small fill-factor”
- Derived from ALPIDE with process modif / depletion



W.Snoeys et al., CERN

■ HV-CMOS

- Not discusses here, see Mu3e

■ Currently

- At the proto (1 cm^2) level
- Demonstrated
 - Full depletion $O(100) \mu\text{m}$
 - Tolerance up to few $10^{15} n_{eq}/\text{cm}^2$

Leptonic e+e- collisions

■ History (20th century <2010)

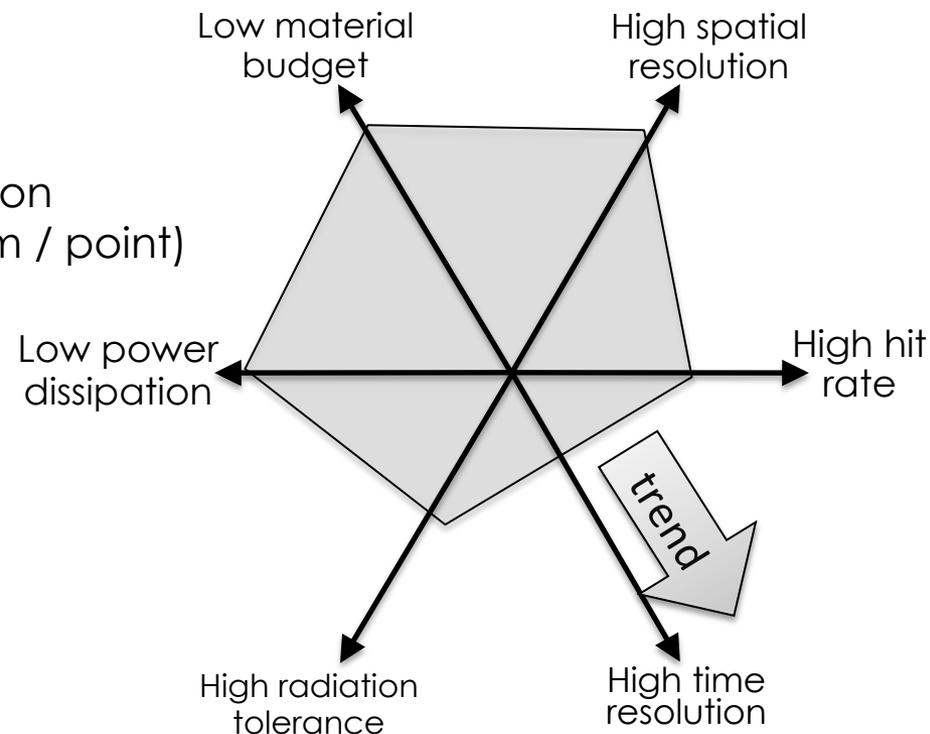
- **SLD** had the first and only CCD-based **vertex detector**
- **LEP** introduced strips and pixel hybrid
- **B-factories** most precise vtx det. so far
- ~10-20 tracks /event, almost no radiation
BUT need for tracking precision (~10 μm / point)

■ SuperKEKB / Belle II (2018)

- x100 luminosity $\Rightarrow \sigma_{\text{time}} \sim 10 \text{ ns}$

■ Next linear colliders (~2030)

- > 100 tracks / event
- Single point resolution $\sigma_{\text{point}} \lesssim 3 \mu\text{m}$
- Material budget **0.1 - 0.2 % X_0**
- Separating primary collision
 - ILC needs $\sigma_{\text{time}} \sim 100 \text{ ns}$
 - CLIC needs $\sigma_{\text{time}} \sim 10 \text{ ns}$



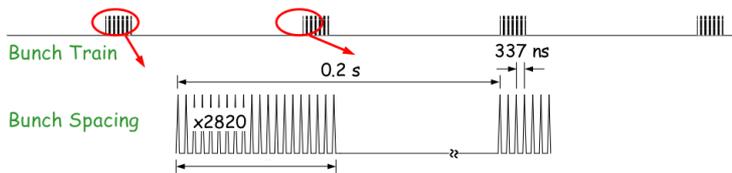
Technical choice

\Rightarrow monolithic

\Rightarrow hybrid if few ns required

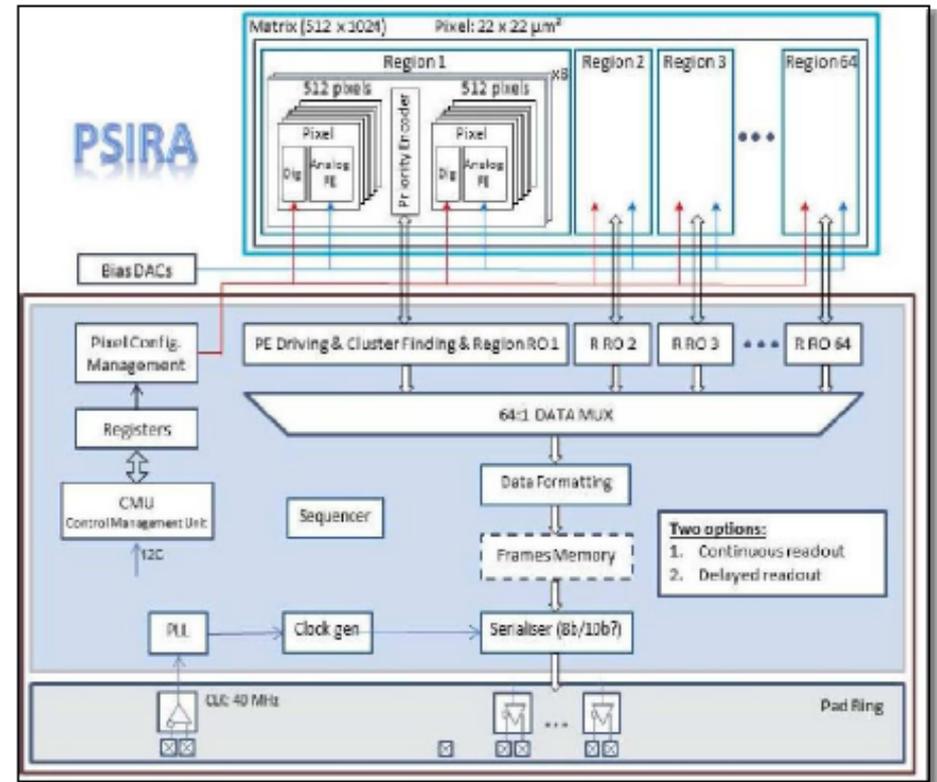
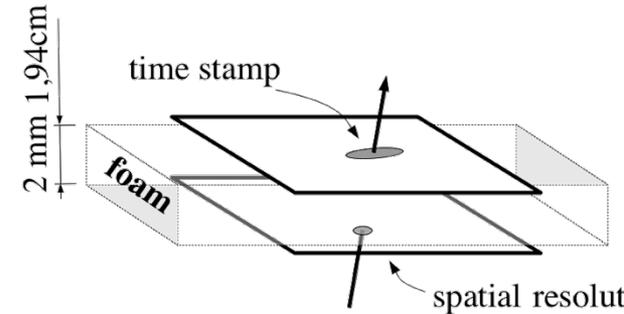
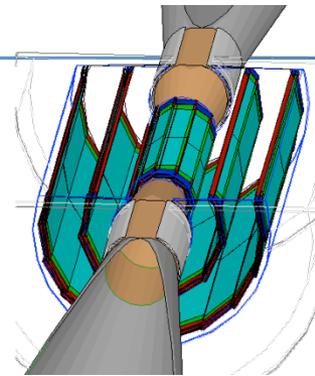
For Vertexing & SiTracker

- Evolution of MIMOSIS
 - Spatial resolution $< 3 \mu\text{m}$
pitch $18 \times 18 \mu\text{m}^2$
 - Power pulsing
to reach $\sim 30 \text{ mW/cm}^2$
- Vertexing: $T_{\text{integration}} \lesssim 1 \mu\text{s}$
- Tracking: $T_{\text{Integration}} 2\text{-}4 \mu\text{s}$



Target sensor readiness by 2025

- Probably smaller feature-size
 $180 \rightarrow 110 \text{ nm}$
- Potentially other foundries
than Tower-Jazz



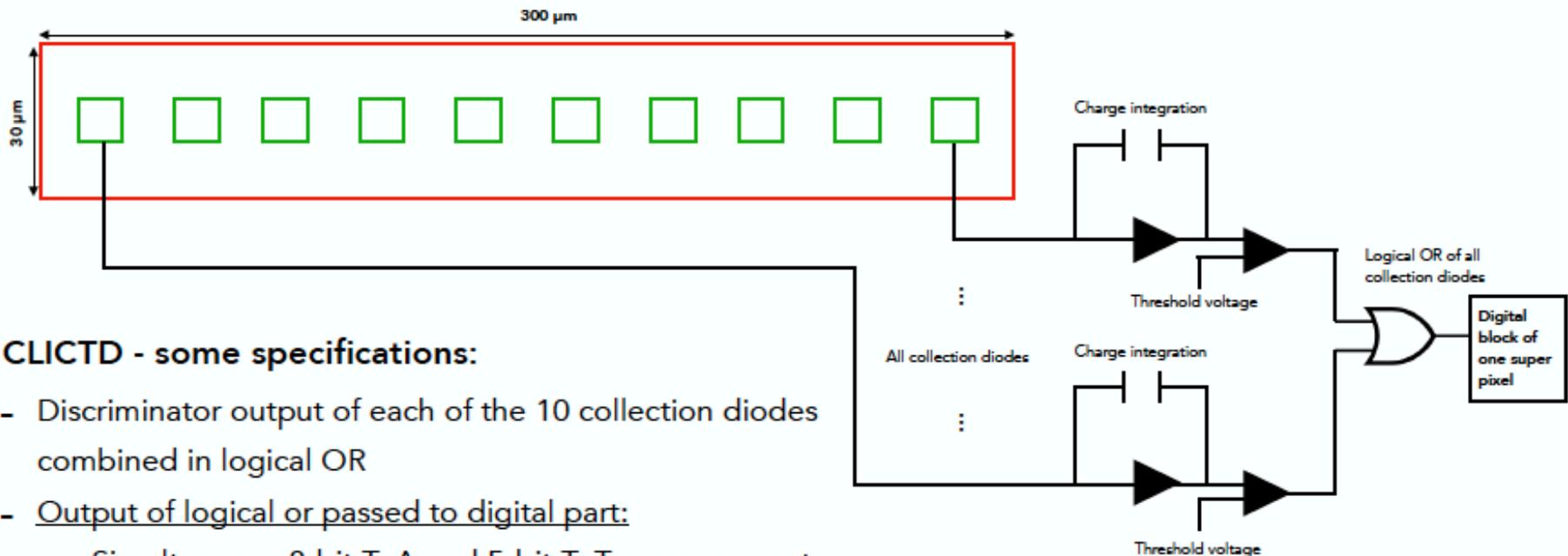
Motivation:

M.Munker, LCWS 2017, Strasbourg

- Promising performance of studied HR-CMOS technology with respect to requirements of CLIC tracker
- Technology used in next phase of R&D to design a fully integrated chip for the CLIC tracker

CLIC Tracker Detector (CLICTD) - main idea/concept for elongated pixels/small strips:

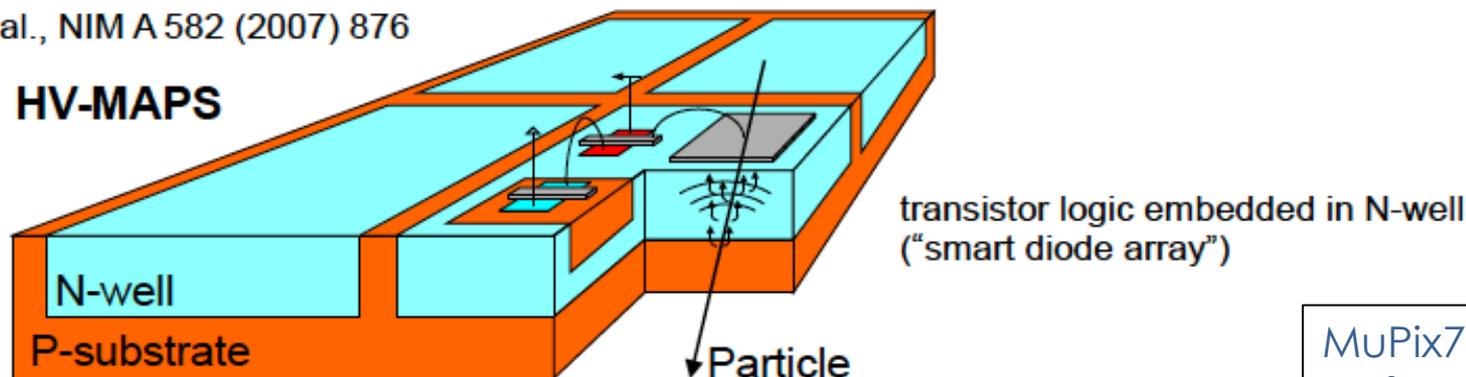
- Design **super pixel structures** to maintain advantages of **small collection diode** (prompt and fully efficient charge collection) while reducing digital logic



CLICTD - some specifications:

- Discriminator output of each of the 10 collection diodes combined in logical OR
- Output of logical or passed to digital part:
 - Simultaneous 8-bit ToA and 5-bit ToT measurements
 - 100 MHz clock to achieve 10 ns time slicing

I.Peric, et al., NIM A 582 (2007) 876



MuPix7 (2016)
• few mm²
MuPix8 final
• 2x2 cm²

High Voltage - Monolithic Active Pixel Sensor (HV-MAPS)

- active sensor → hit finding + digitisation + zero suppression + readout
- high precision → pixels 80 x 80 μm²
- low noise ~ 40 - 50e → low threshold
- small depletion region of ~ 10 μm → thin sensor ~50 μm (~ 0.0005 X₀)
- standard HV-CMOS process, 60 - 90 V → low production costs
- continuous and fast readout (serial link) → online reconstruction

Tracking in HEP: Systems

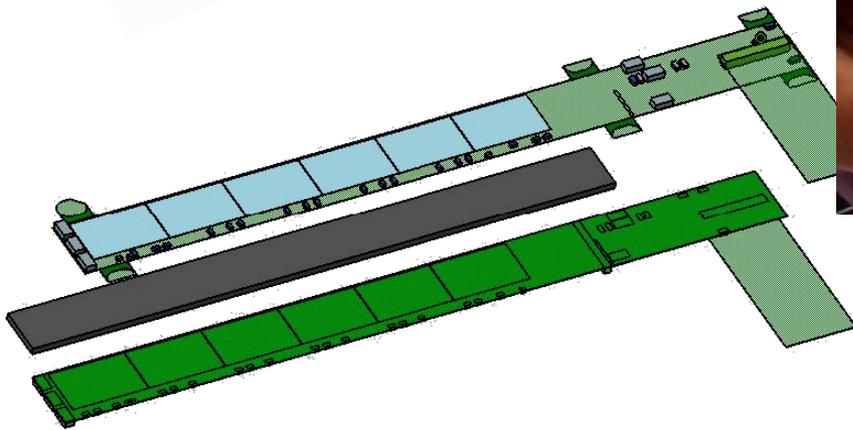
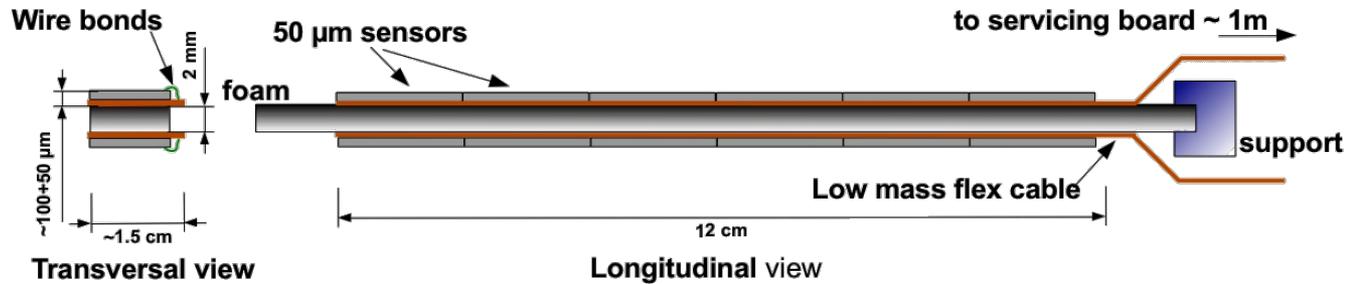
Proof that MAPS are easily integrated

Layers for the ILC-vtx

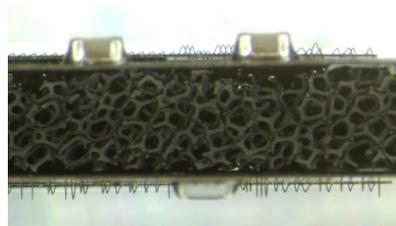
■ PLUME project



- DESY-Hambourg,
Uni. Bristol,
IPHC



Two position measured
Thickness 2 mm
8 Mpixels, 100 μ s, 10 g
9 Watts (air cooled)



Side view

Single Arm Large Area Telescope

■ Basic sensor

- MIMOSA-28 thinned to 50 μm

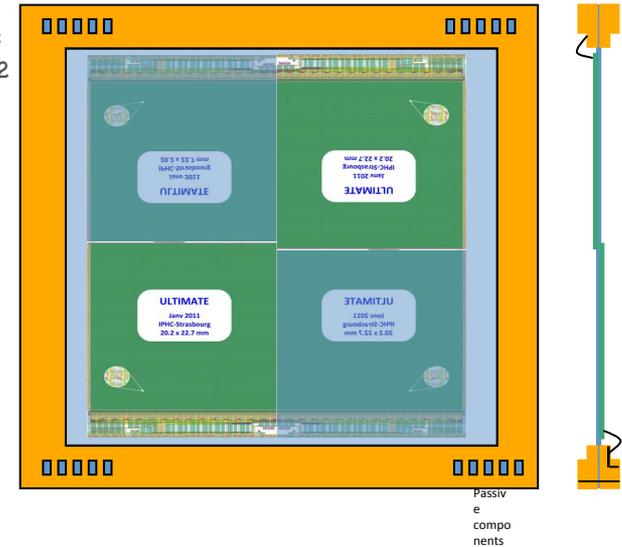
■ Assembly

- stretching 50 μm -thin Mylar foil
- gluing 2 staggered sensors on each side

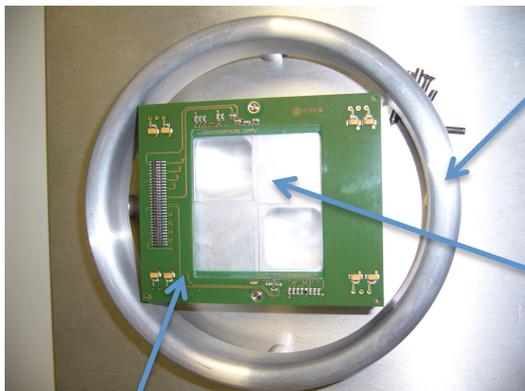
■ Basic numbers

- 3.6 Mpixels over 15.3 cm^2
- 190 μs integration time
- cracks = central vertical band about 100 μm

Sensing area =
 $4 \times 3.8 \text{ cm}^2$



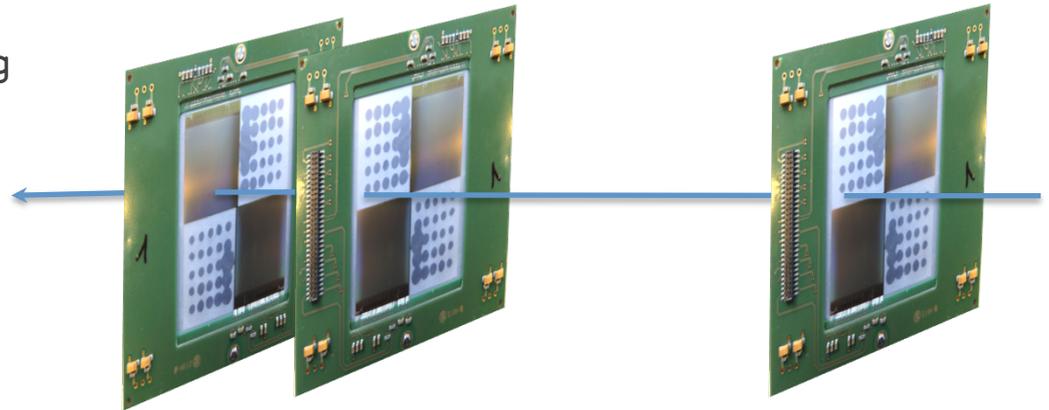
Telescope configuration



Stretching frame

Mylar foil

Mechanical & electrical support



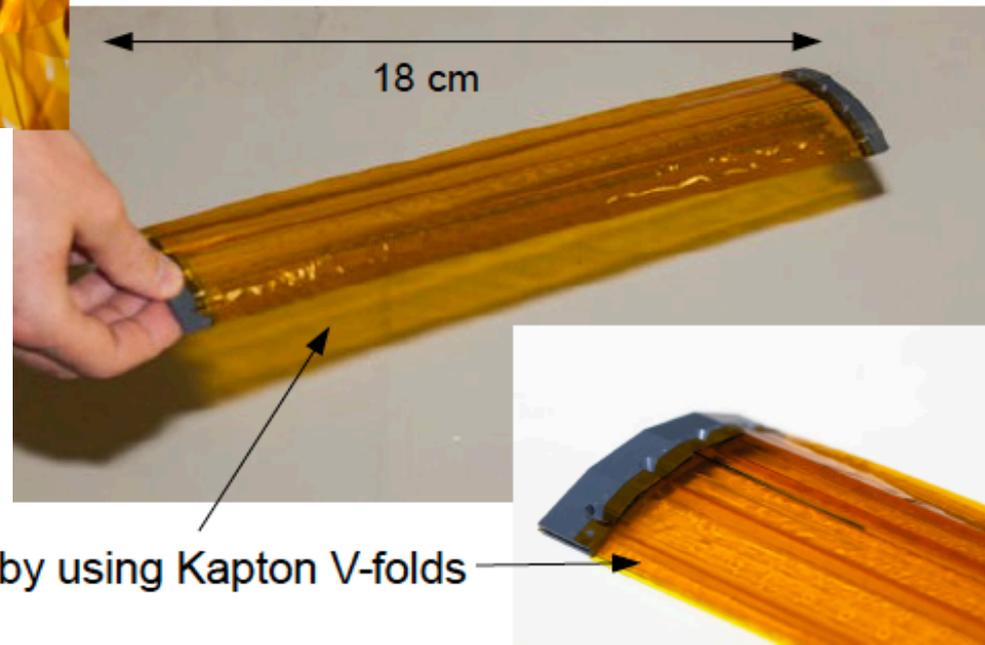
Mu3e – VTX concept



Ultra-thin mechanical mockup:

- sandwich of 25 μm Kapton[®]
- here 50 μm glass (instead of Si)

Even larger stable structures possible



Sandwich design:

← monolithic HV-CMOS sensor (50 μm)

← thin aluminium / kapton flexprint

← kapton support foil (25 μm)

+ gaseous helium cooling

He

$X \leq 0.1\% X_0$ per layer possible

by using Kapton V-folds

André Schöning, Heidelberg (PI)

25

Vertex2016, September 27, 2016

Non tracking applications

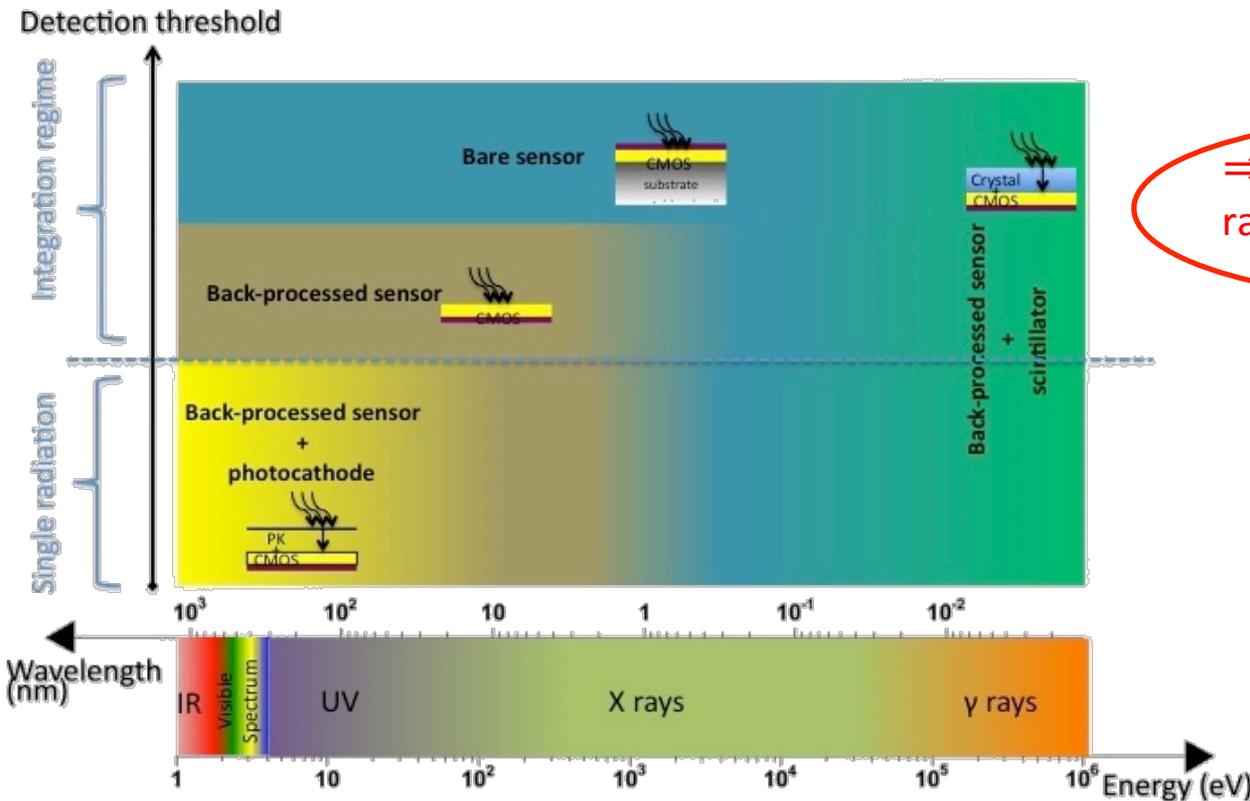
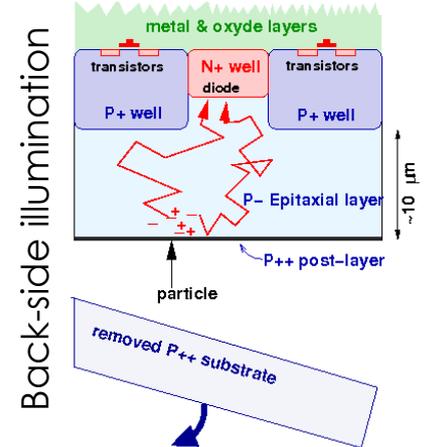
- *Calorimetry !*
- *Molecular imaging*
- *X-ray counting & spectrometry*
- *Autoradiography*

Sensitivity to radiations

Charged particles

- Low ENC \rightarrow easy detection for $E_{\text{loss}} \sim \text{keV}$
- Sensitivity to all spectrum
 - Limitation to low penetrating part. (e- of few keV, α)

Photons

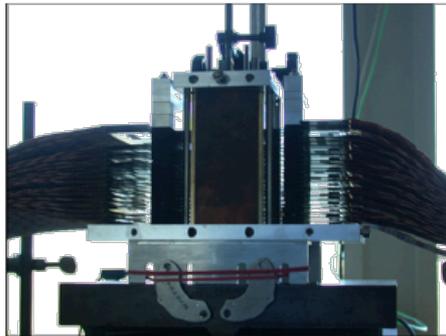


\Rightarrow Sensitivity depends on radiation stopping power

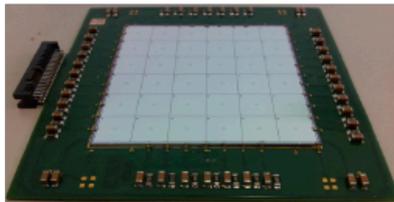
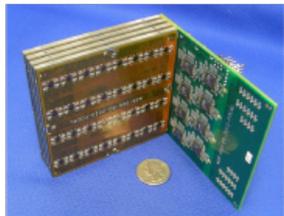
High-Granularity digital electromagnetic calorimetry

- Stack of (tungsten + MAPS) layers

24 layer pixel detector



Pad layer integration



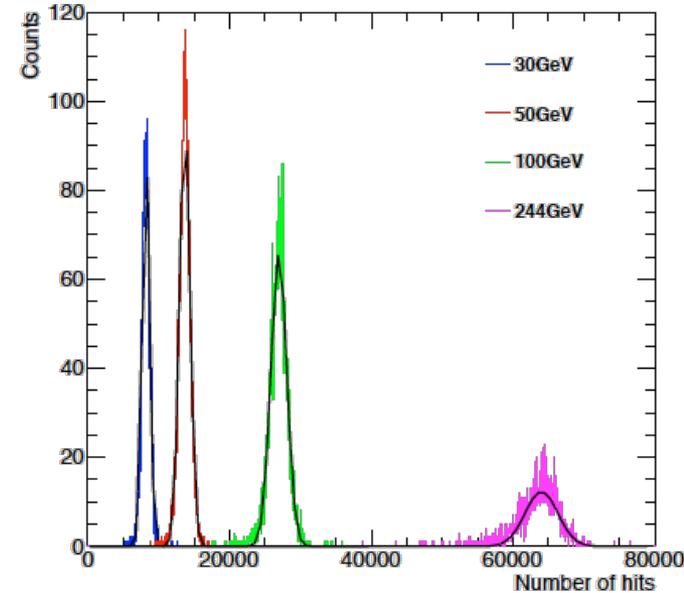
R&D Activities with Si-pad/W Calorimeter Prototypes (Japan/ORNL, India) not covered here

Several groups involved:

Full prototype with pixel detectors
 CMOS (MIMOSA) 39M pixels,
 30 μ m pitch
 use synergy with R&D for ALICE ITS
 upgrade
 Full prototype with pad readout

Performed systematic tests:

Test beam data from 2 to 250 GeV
 (DESY, PS, SPS)
 Cosmic muons



- response to electrons
 from SPS test beam

- calculated from per-event hit density
 distributions

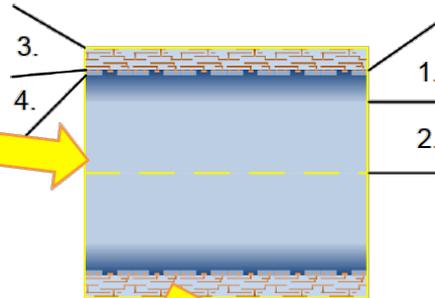
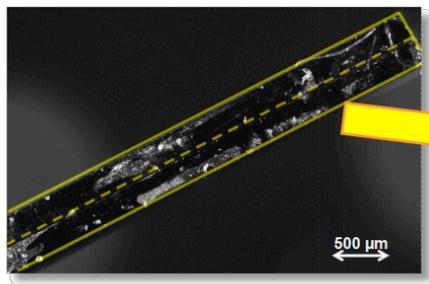
Utrecht/Nikhef (Netherlands),
 Bergen (Norway),

Tsukuba, Nara, Hiroshima (Japan),
 ORNL (US)
 VECC Kolkata,
 BARC Mumbai (India)

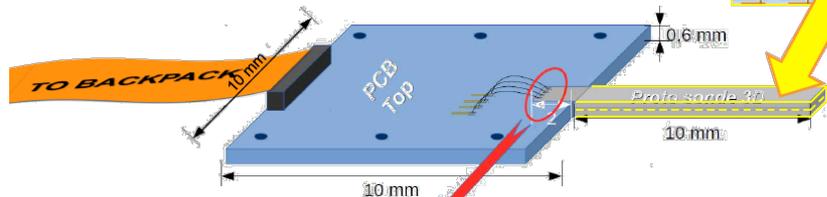
Charged particles dosimetry

■ Molecular imaging with β^+ emitters in moving rodent

- MAPSSIC: extreme integration in specific environment
 - Constraint on size and power dissipation
 - IMNC, IPHC, CPPM, CERMEP, NeuroPSi
- Exploit CMOS sensors derived from ALICE
 - One active probe = 160 μ W
 - For few counts / s
 - Wireless connection

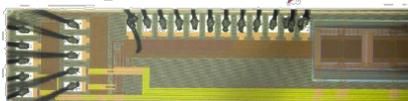


probe in the brain :
- section $\sim 500 \times 500 \mu\text{m}^2$
- sensitive volume (18 μm) immune to γ



1. Epi-layer (18 μm)
 2. P-type Substrate
 3. Metallization ($\sim 10 \mu\text{m}$)
 4. Process
- 1.+2.+3. $\sim 250 \mu\text{m}$

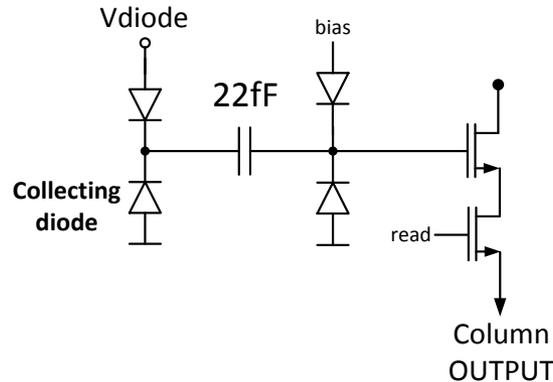
Same wire-bonding on both sides



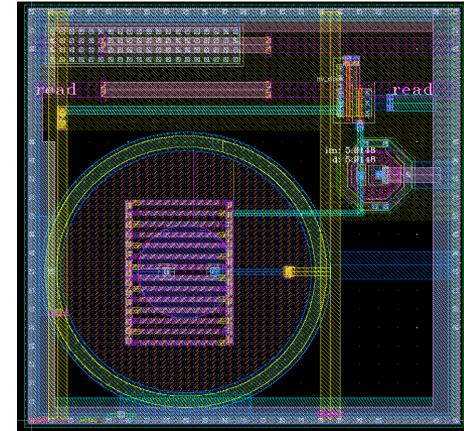
Currently integrating prototype sensor ...

Depletion on prototype sensors

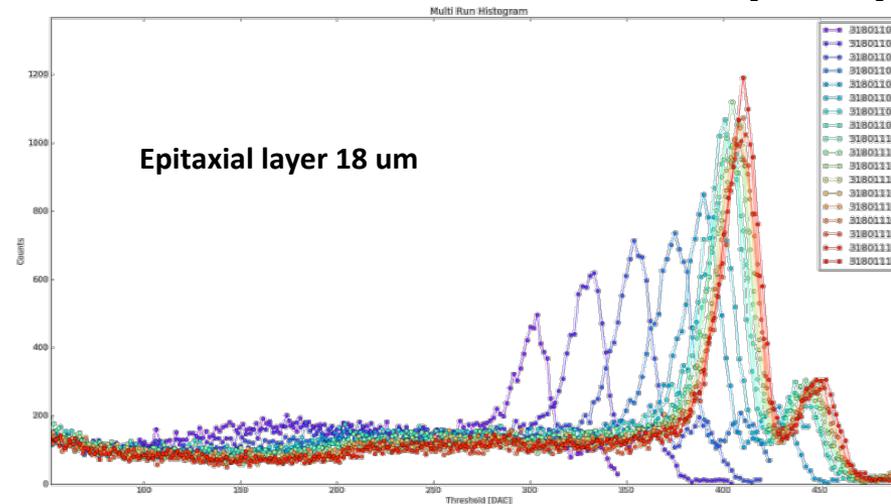
■ PIPPER-1 (2014), PIPPER-2 (2016), PIPPER-3 (2017)



- Prorotype chip 32 x128 pixels
- Analog outputs
- Pixel size 22x22 μm
- **AC coupled collecting diode**
- Produced on two substrates:
 - Epitaxial layer 18 μm
 - Czochralski substrate



⁵⁵Fe irradi. function of diode bias (1-19V)



Energy resolution

After clustering → Seed pixel distribution

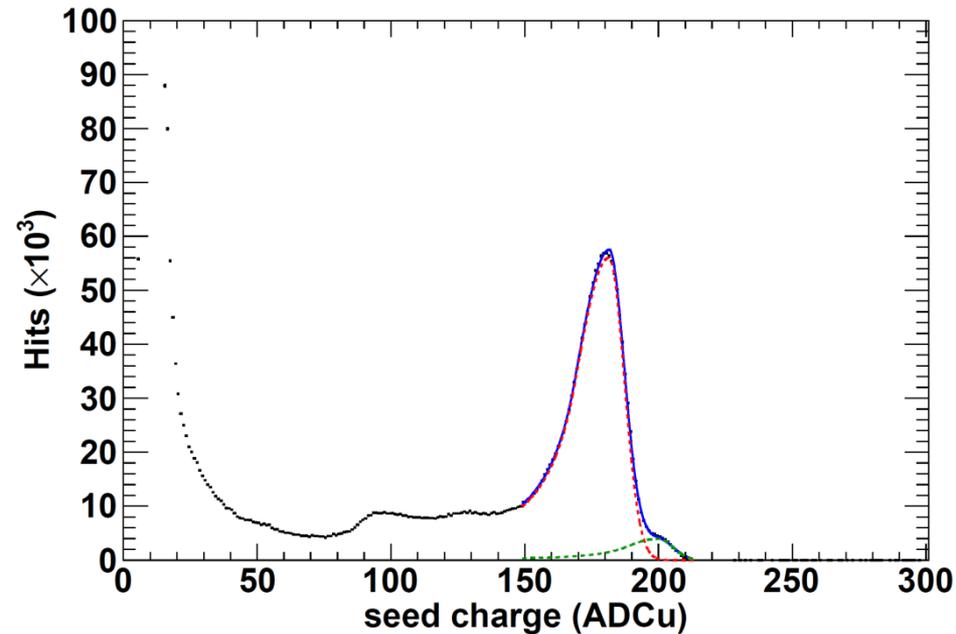
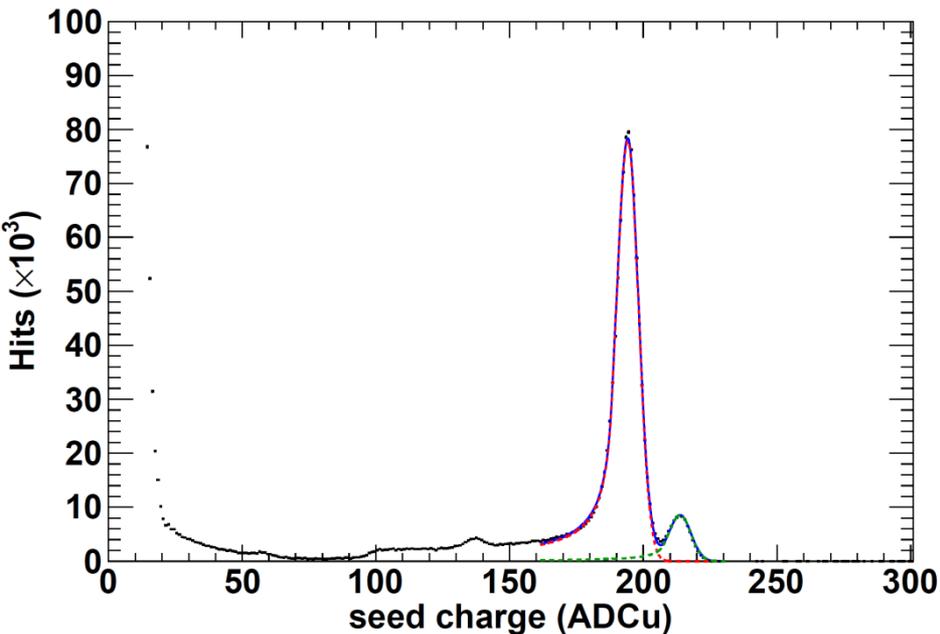
- Energy resolution dominated by collection fluctuation on charge coll. (full thickness sensor)

○ HR-18

- ENC = 24 e⁻ (eq to FWHM ~200 eV)
- FWHM (5.9 keV) = 298 eV
- 30.38 eV/ADCU
- Si escape peak visible (138 ADCu)
- 75 % charges collected on the seed pixel

○ CZ

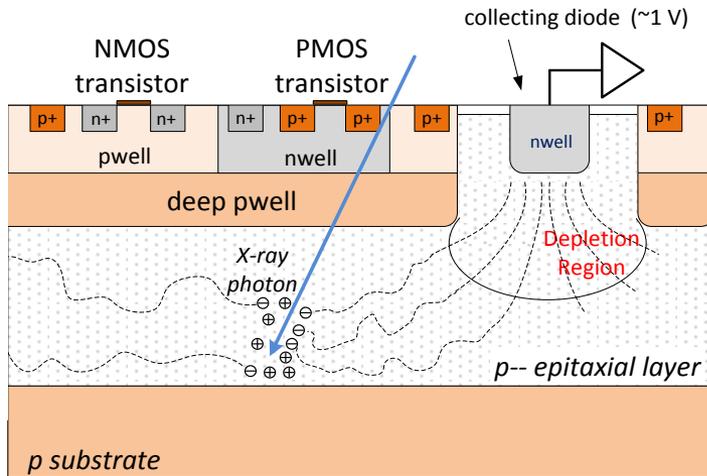
- ENC = 26 e⁻
- FWHM (5.9 keV) = 686 eV
- 32.51 eV/ADCU
- Mn-K α and Mn-K β merging
- 68 % charges collected on the seed pixel



Pipper-2 measurements (presc. 2, T_{cool} = 7 °C, V_{diode} = 30V) ⁵⁵Fe irradiation – 400000 frames

Engineering the sensitive layer

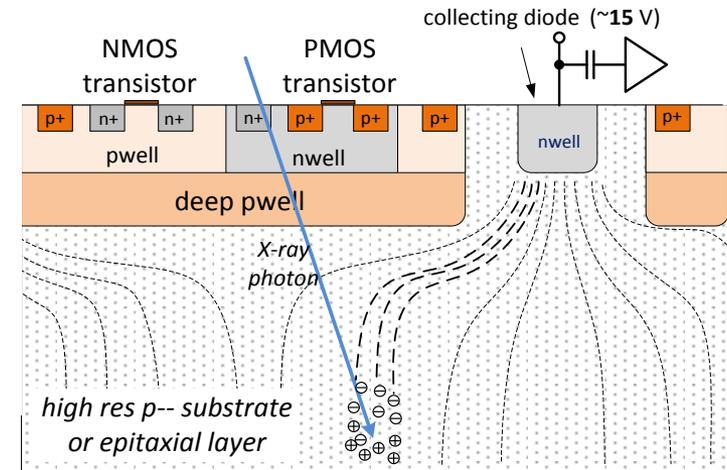
Low-resistivity layer (the std old way)



Charges move MOSTLY from therm. diffusion

- Long (~100 ns) collection time
- Important charge sharing

Depleted MAPS (the new way)



Charges move MOSTLY from E drift

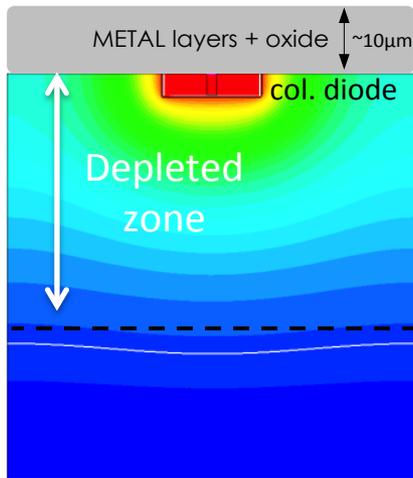
- Short (< 10 ns) collection time
- Low charge sharing

Back-side illumination

- Substrate removed (50 μm easy in industry)
- Sensors too thin (~20 μm) \rightarrow front support
- Complex connexion (costly)
- Could stay thick \rightarrow no complexity

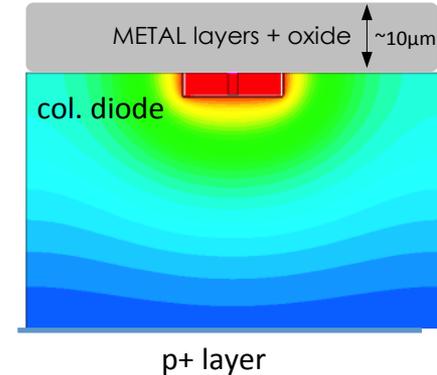
Back Side Processing

■ Goal: « costless » BSI sensor

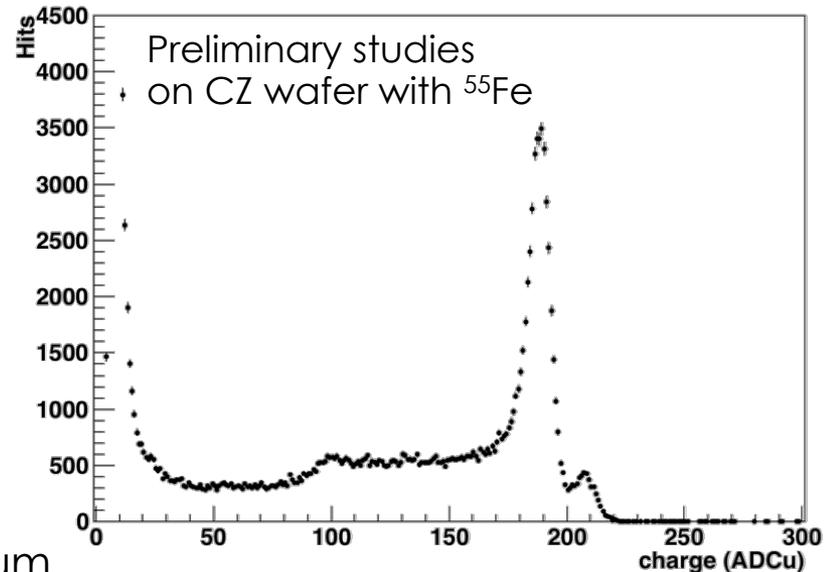


[J. HEYMES]

- Thinning 50 µm
- Ion implant
- Annealing



Post processing done in Jan 2017

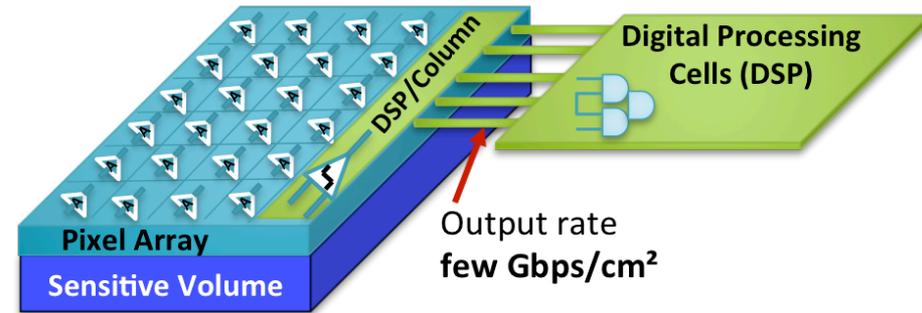


➔ Depletion depth under investigation: 25-40 µm

Photon counting?

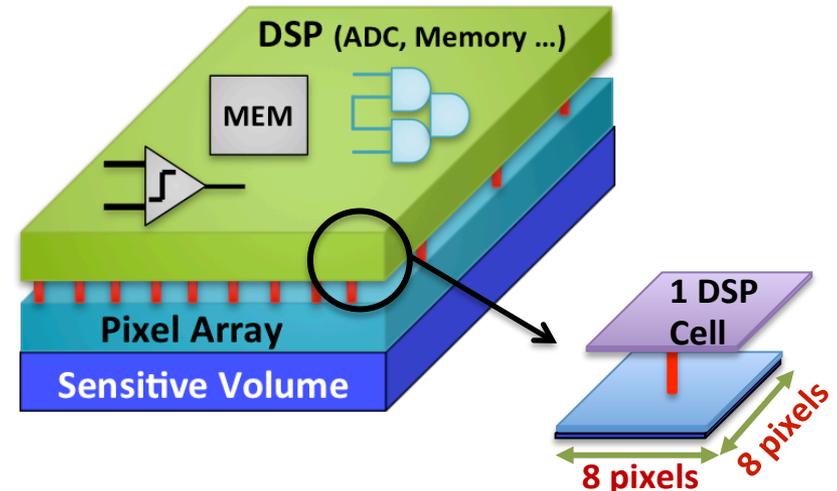
■ 2D architecture

- 1 sensor = **SYNAPS-2D**
- Rolling shutter with // columns analogue signal readout
 - 100-200 ns readout per row
 - About 512 rows
- Digitization (binary) at column end with energy window
- Dynamic range $1-2 \times 10^4$ photons/pixel/s



■ Mid-term → 3D architecture

- 1 sensor + 1 DSP chip = **SYNAPS-3D**
- Local rolling-shutter within submatrix
 - 1 μ s readout per submatrix
 - ~ 10 photons (5 keV) dynamic per pixel
- Digitization + Memory in DSP
- Dynamic range $1-10^7$ photons/pixel/s



Prototype small pixel X-ray counter

Counting Low energy X-ray - Mimosa 22SX

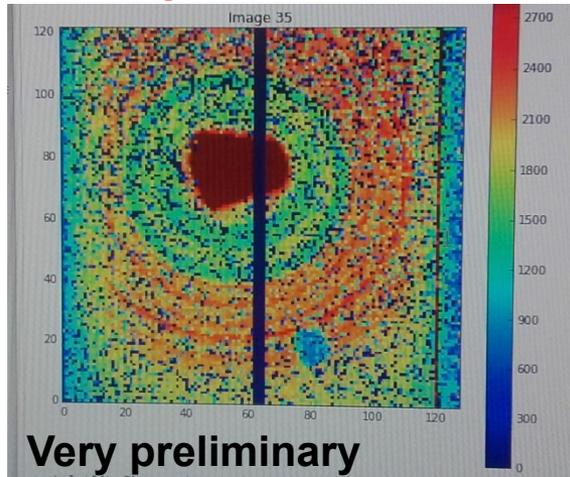


Requirements:

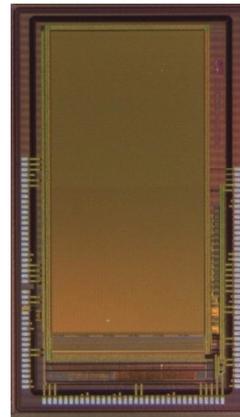
- X-Ray Energy Range [few 100 eV – 5 keV] with 100% QE
- Counting Dynamic [1-10⁷] ph/pix/s
- High Spatial Resolution (pixel pitch ~ 20 μm)

Test at HERMES beam-line

- F.Orsini *et al.*
- Simple pin-hole diffraction
- Low energy, down to 1 keV

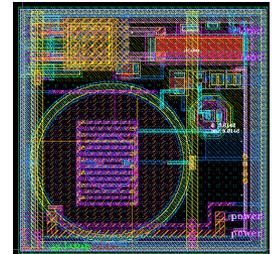
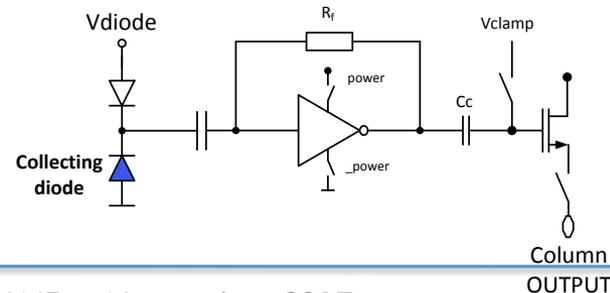


Mimosa 22SX



First 2D prototype specs

- Tower Jazz 180 nm CIS
- 128 x 256 pixels with 22μm pixel pitch
- Collecting diode AC coupled to the amplifier
- Discriminator with 2 thresholds → energy windowing
- Binary outputs
- 16 mm² of active area



A spin-off application for M22SX

■ Dose Monitoring by counting



CYRCé Cyclotron at IPHC:

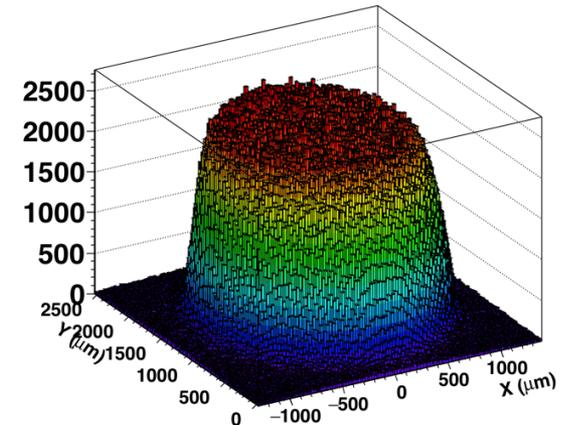
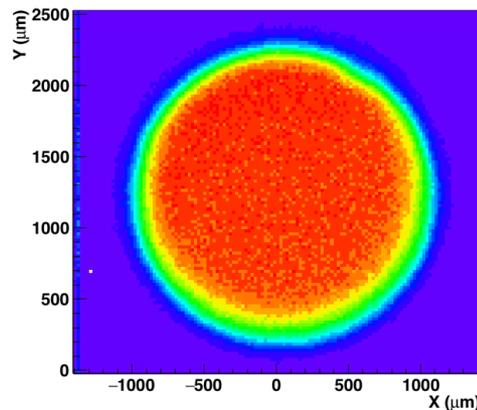
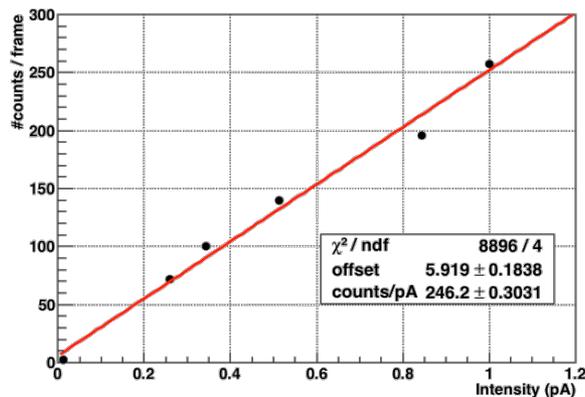
- 24 MeV protons
- Millimetre beam size for small animal proton therapy

Motivation:

Monitor dose for small beam size (problematic with current detector)

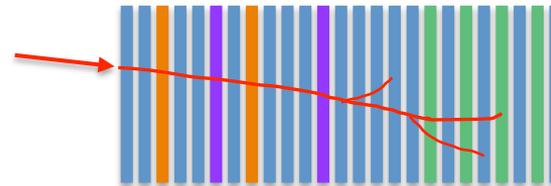
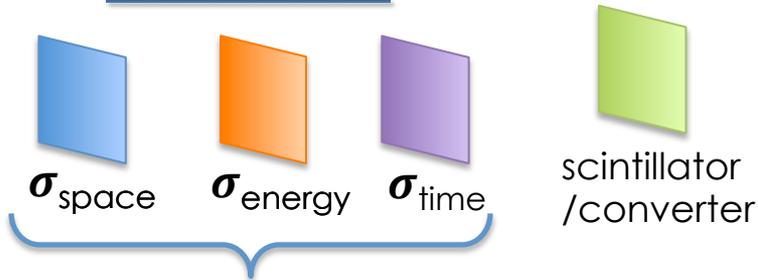
First tests with Mimosa 22SX

- Linear behaviour in the measured fluence range
- At least 1000 protons/pix/s possible



DREAM of electronic emulsion

Let's stack!



CMOS pixel flavours with sense layer ~ 100 % thickness

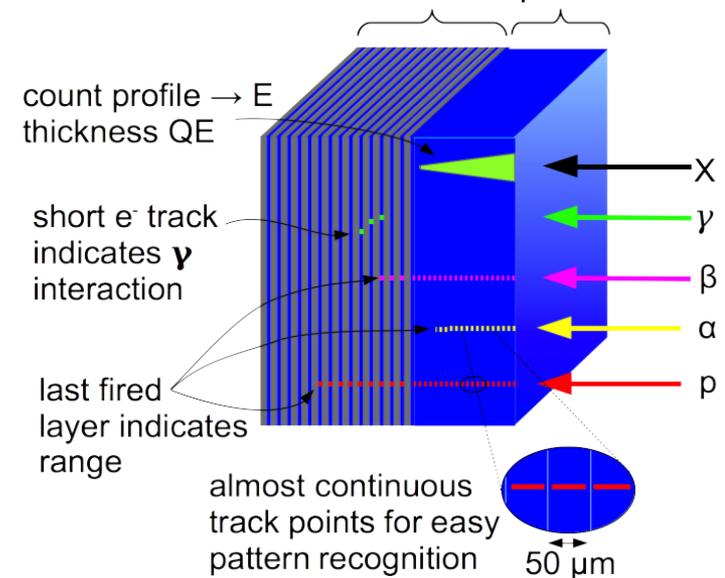


Fast electronic equivalent of a nuclear emulsion

- **8D measurements**
 - 3D position + 3D direction
 - 1D time
 - 1D energy (range / sampling)
- **Adjustable performances**
 - Stack re-shaping (sensor redesign)

“Calorimeter” Tracker

mixed scint. + Si sensors pure Si sensors



■ Historical perspective

- CMOS Image sensors started ~60 years ago
 - ➔ customisation into the Si sensor world
- Scientific version of CIS (sCMOS) started ~ 20 years ago
- CMOS pixel sensors (MAPS) for charged particle tracking started ~ 20 years ago
 - Very few labs in the high-energy physics community

■ Currently a lot of activities

- CMOS processes are evolving quickly + corresponding integration technologies
- Many labs and design companies are pushing various performances
 - Ex: spectrometry, electron multiplying CMOS, ...
- In Strasbourg, 2 architectures emerging:
 1. Fast binary outputs
 2. Energy deposited measurement outputs

■ Outlooks

- More applications to be expected
- **Complex landscape**, time to know what you want (cost, specs, ...)

ADDITIONAL SLIDES



CMOS Image Sensor (CIS)

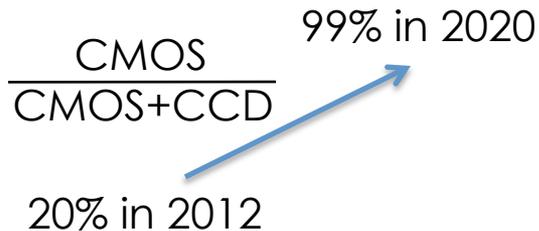
■ Main markets

- Customers (camera, smartphone, ...)
- Industry (machine, automotive, ...)
- Medical imaging

Pixel size 1-2 μm
Frame rate ~ video
Integration camera (~~single-quantum~~)

→ Main markets = technology drivers

■ CCD vs CMOS



- CMOS camera yield > few billions/year
- Main reason: **cost** and now **performances**

■ Foundry examples

• **SONY**

- Main world player
- Ex: Backside illuminated sensor "stacked" camera (sensor + readout)
- 60000 wafers / month

• **Tower-Jazz**

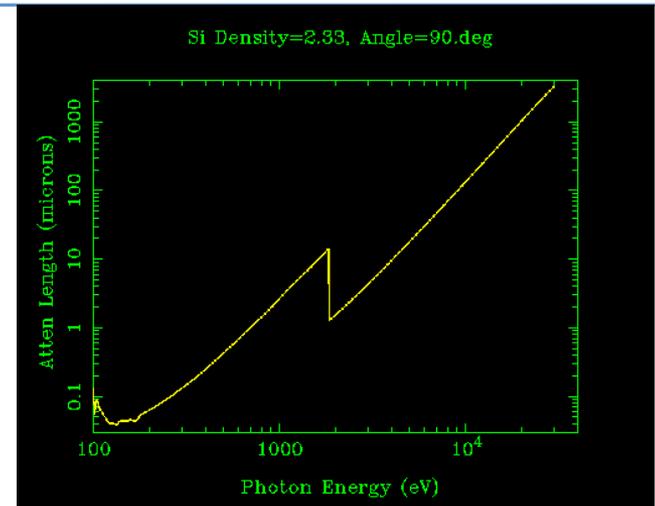
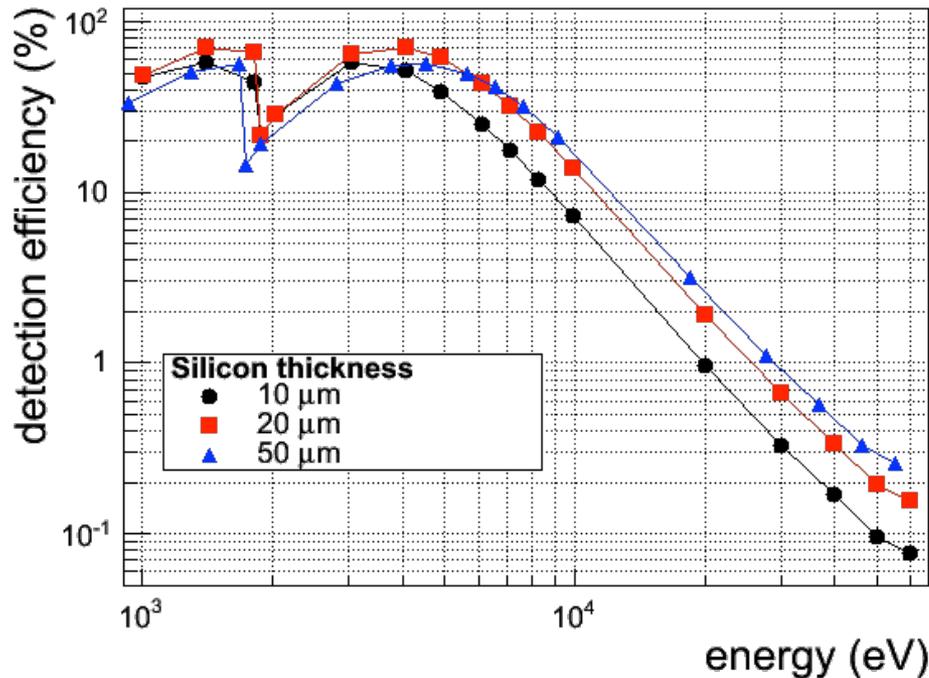
- Small & very focused player
- Ex: Medical application sensor
- Few 1000 wafers / year

X-ray detection

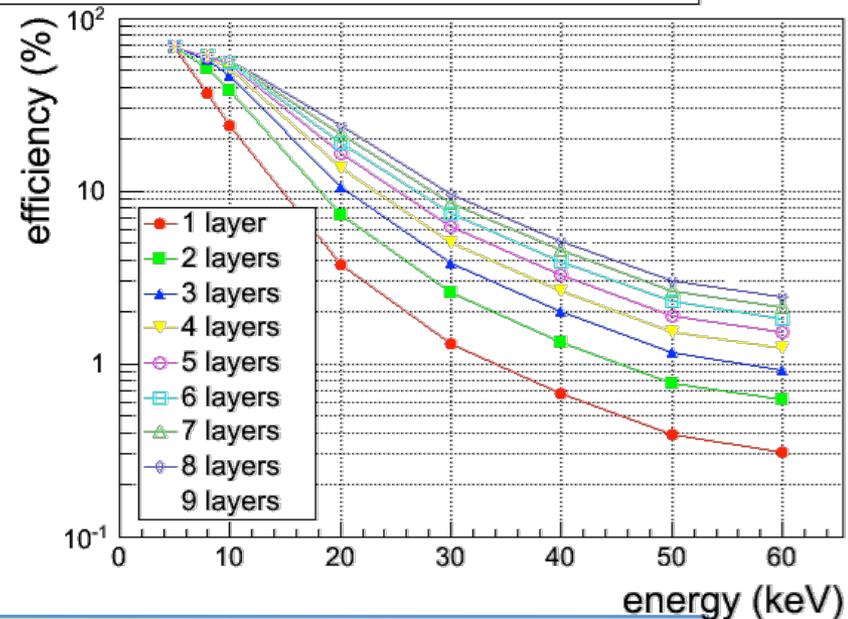
■ Silicon weak point

- μ drops quickly with E

Beer-Lambert law: $1 - e^{-\mu x}$



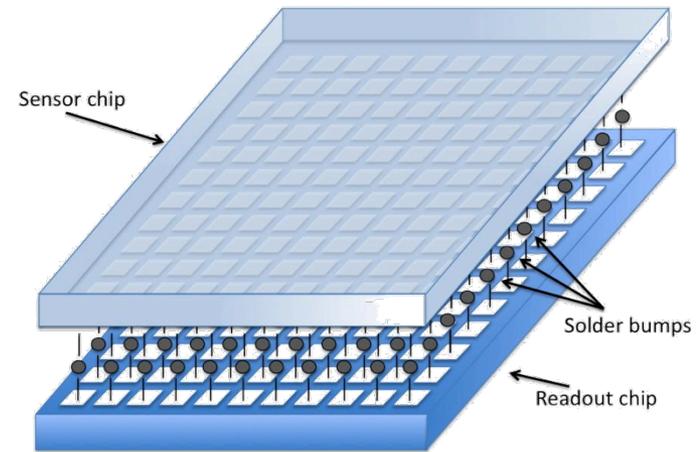
Efficiency wrt energy for 40 μm thick layer



Hybrids (strips & pixels)

■ THE standard approach in HEP

- Implement powerful processing
 - Pre-ampli + shaper \Rightarrow time & energy resol.
- Radiation hardness
 - Si type adapted
 - 3D sensors
- Recently edgeless sensors

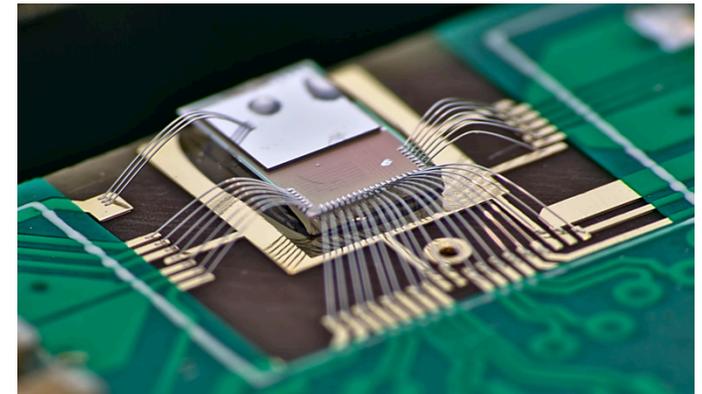


■ “limitations” / pixels

- Relatively large pixel size
 - Limited by bump-bonding & processing
 - Current ATLAS $50 \times 250 \mu\text{m}^2$, CMS $100 \times 150 \mu\text{m}^2$
- Relatively thick \Leftarrow 2 thickness of silicon
- Sensitivity to low ionizing particles
 - Typical minimal threshold $\sim 1000 e^-$

■ Developments / CLIC

- targets pitch $25 \times 25 \mu\text{m}^2$
- with thickness $50 \mu\text{m}$ (ASIC) + $50 \mu\text{m}$ (Sensor)
- Some functional prototypes



■ A “monolithic” approach

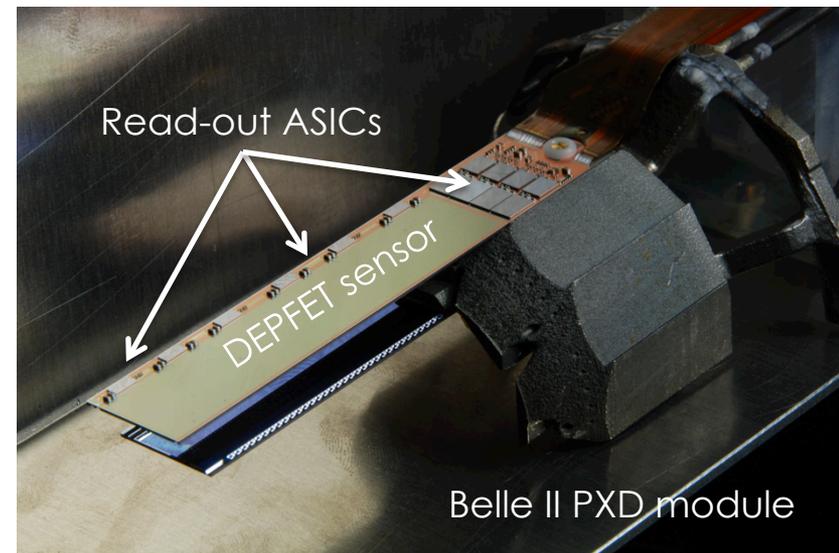
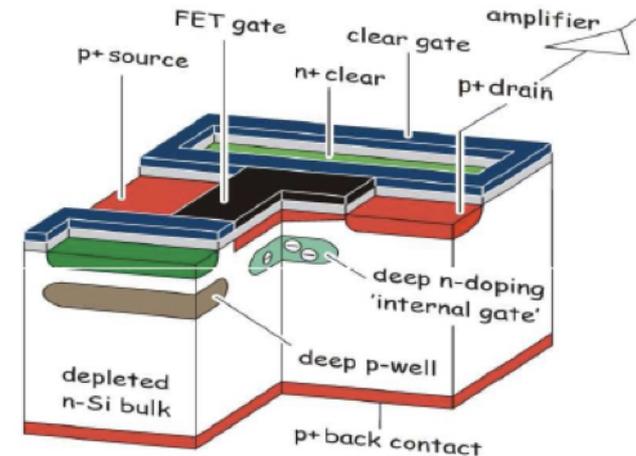
- Driven by imaging (X-rays, electrons)
- Amplification in-pixel but no processing
- Fully depleted volume
300 to 50 μm (thinned)

■ First detector for HEP in 2018

- Belle II vertex detector (PXD)
- The thinnest detector **0.18 % X_0 / layer**
- Pitch not crucial: 70 μm
- 20 μs integration/read-out time

■ Toward ILC

- Smaller pixel **20 μm**



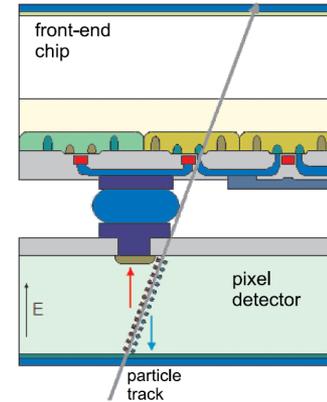
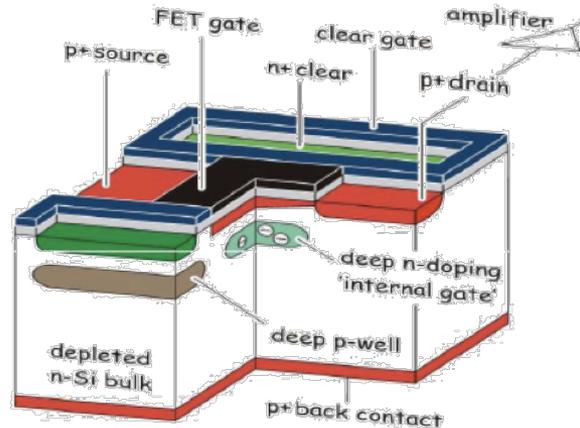
Pixel detectors in HEP (except MAPS)

■ CCD

- Very seldom used
- Too slow & weak / TID, NIEL

■ DEPFET

- First application on-going
- Small pixels possible
- Fully depleted sens. Layer
- Internal amplification BUT
 - needs read-out chips
 - speed limited
- Production site limited

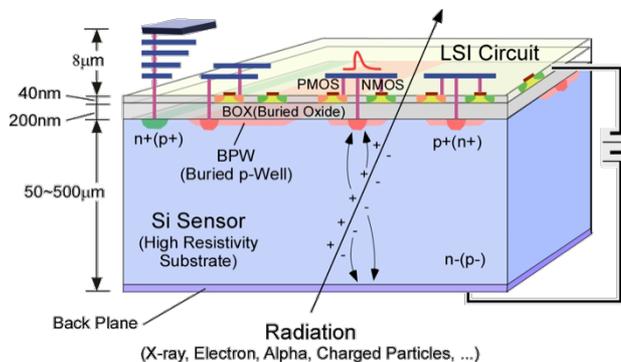


■ Hybrid pixel

- THE standard way
- Small pixel hardly possible
- Fully depleted sens. Layer
- Sens volume decoupled from processing layer
 - Sensitivity limited
- FEE on top of sensor
 - Increased mat. budget
 - BUT powerful processing ⇒ FAST
- Bump bonding costly

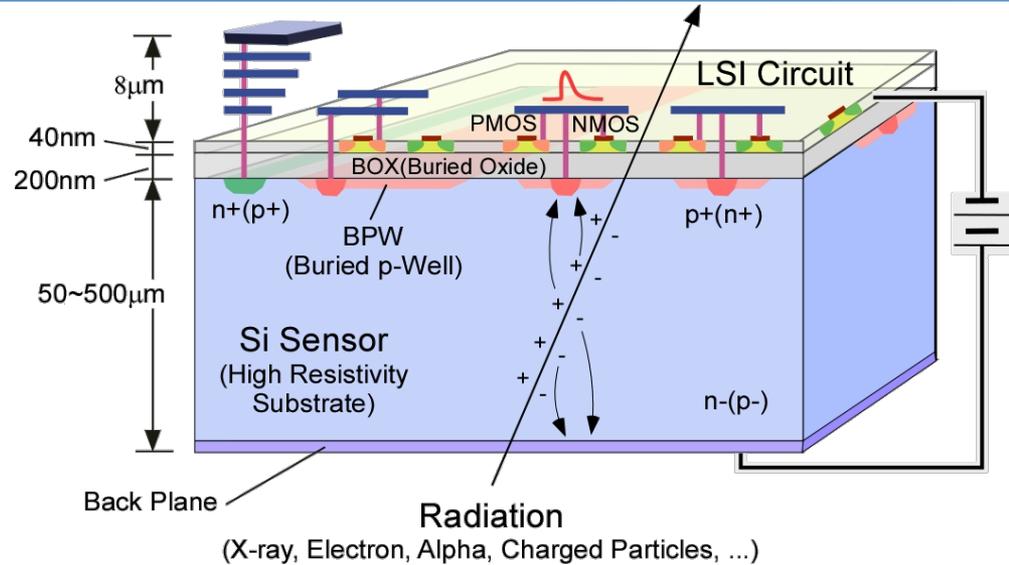
■ Silicon On Oxide (SOI)

- Never used yet
- Small pixel possible
- Fully depleted sens. Layer
- Embed processing
- Sens volume decoupled from processing layer
- TID issue solved (?)
- Costly (?) process



■ A monolithic-hybrid ?

- Includes **fully depleted** sensitive layer 50-700 μm
- Includes **processing power**
 - less constraint / CMOS sensors
- Large SNR
- Relatively weak to radiation
 - thick oxide

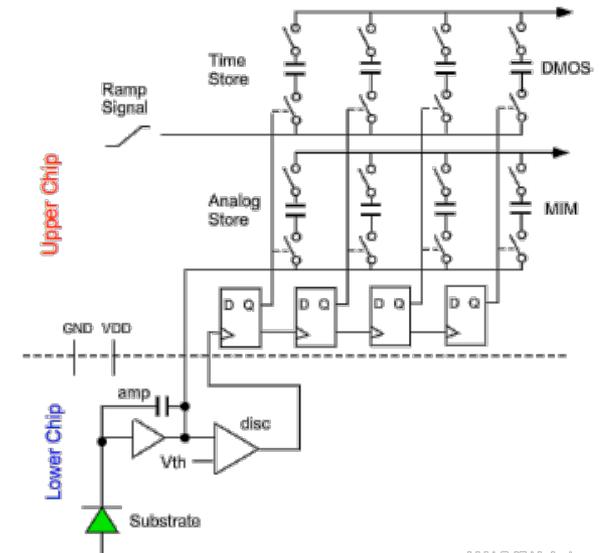


■ Current usage

- Mostly for imaging (X-rays)
 - Synchrotron, medical, astronomy, ...

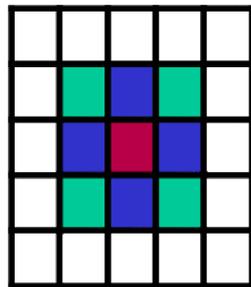
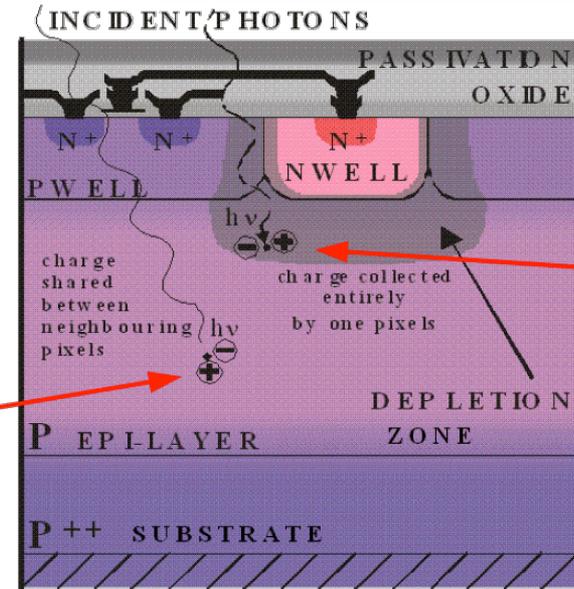
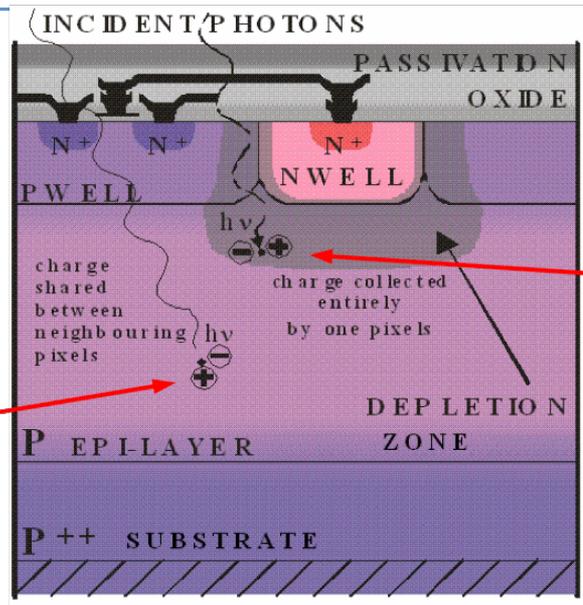
■ Project in HEP: ILC

- Enhanced signal treatment within 20 μm pixel
 - **Spatial & time resolution**
- Still prototyping



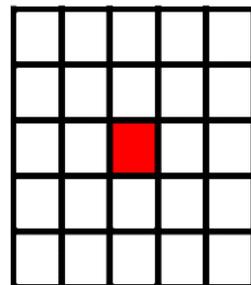
2016.7.27 Y. Arai

Non depleted MAPS



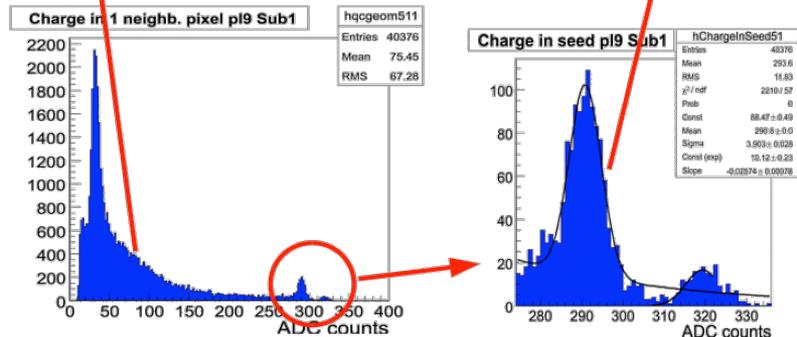
Cluster of hit pixels:

Σ signals ~ all X-ray energy & low signal on central pixel



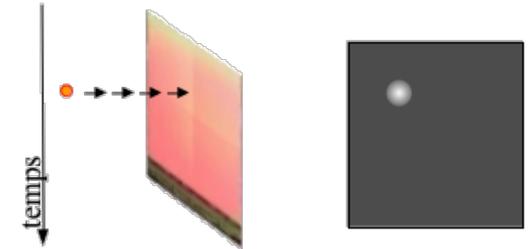
Single hit pixel:

Signal = all X-ray energy (calibration)



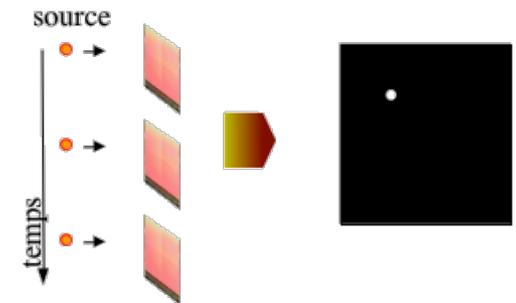
■ Std imaging sensors \Leftrightarrow usually **INTEGRATION**

- One channel signal = several quanta of radiations
- Key parameters:
 - dynamic (full well), point spread function, noise
- Single frame \sim 100% occupied
 - read-out relatively slowly (\sim video rate)



■ Tracking sensors \Leftrightarrow **COUNTING** single particles

- One quanta = several channels
- Key parameters:
 - resolution (E, t, position), SNR, dark count
- Single frame \leq 1% occupied
 - read-out @ high-frequency ($<$ 10 kHz)

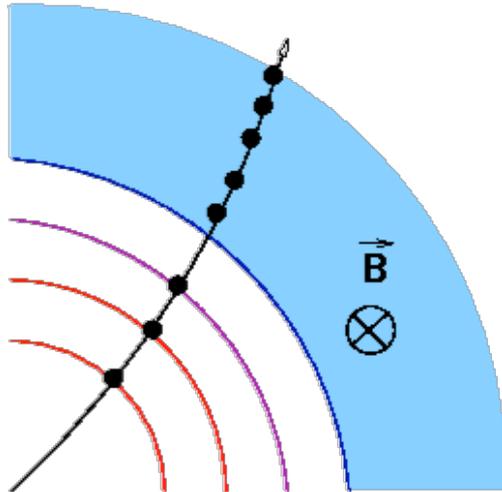


- ➔ Both can build image...with various qualities
 - Strong impact on read-out electronic design

Tracking in High Energy Physics

■ Multi-layers are needed

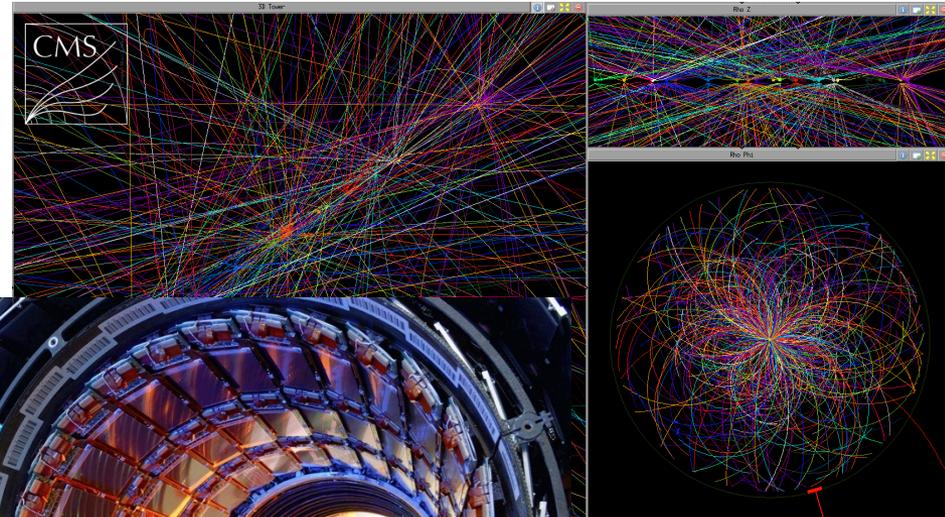
- Material budget (thickness) to be limited $\ll 1\%$ radiation length (X_0)
- Power dissipation is a problem



■ Events are complex...

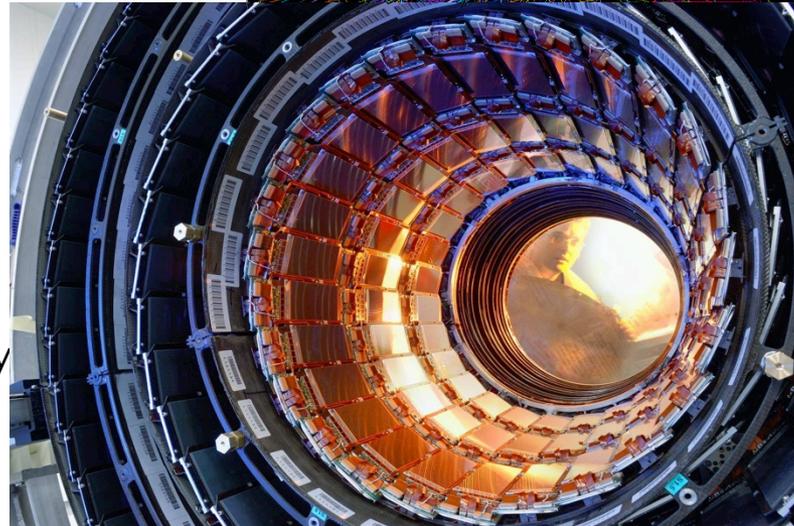
- Spatial resolution (2-20 μm)
- Time resolution (ns to μs)

... BUT (almost) EMPTY wrt sensors



■ LHC-CMS tracker

- Full silicon technology
- 210 m^2
- 9.6×10^6 channels
- few 10 Tbits/s



■ Scientific CMOS (sCMOS)

- Improved CIS
- Essentially integrating detectors
 - Increased dynamic (full well)
- Target generic applications

- Keep small pixels (few μm pitch)
- Speed up to 1000 kframes/s
- Sensitivity
with equivalent noise \sim few e^-

■ MAPS

- Monolithic Active Pixel Sensor
- Only counting detectors
 - single quanta
- Target specific experiment

- Pixel size adapted
to desired resolution
- Speed adapted to
occupancy
- Equivalent noise \sim 10-30 e^-

Signal & Noise build-up

■ Signal

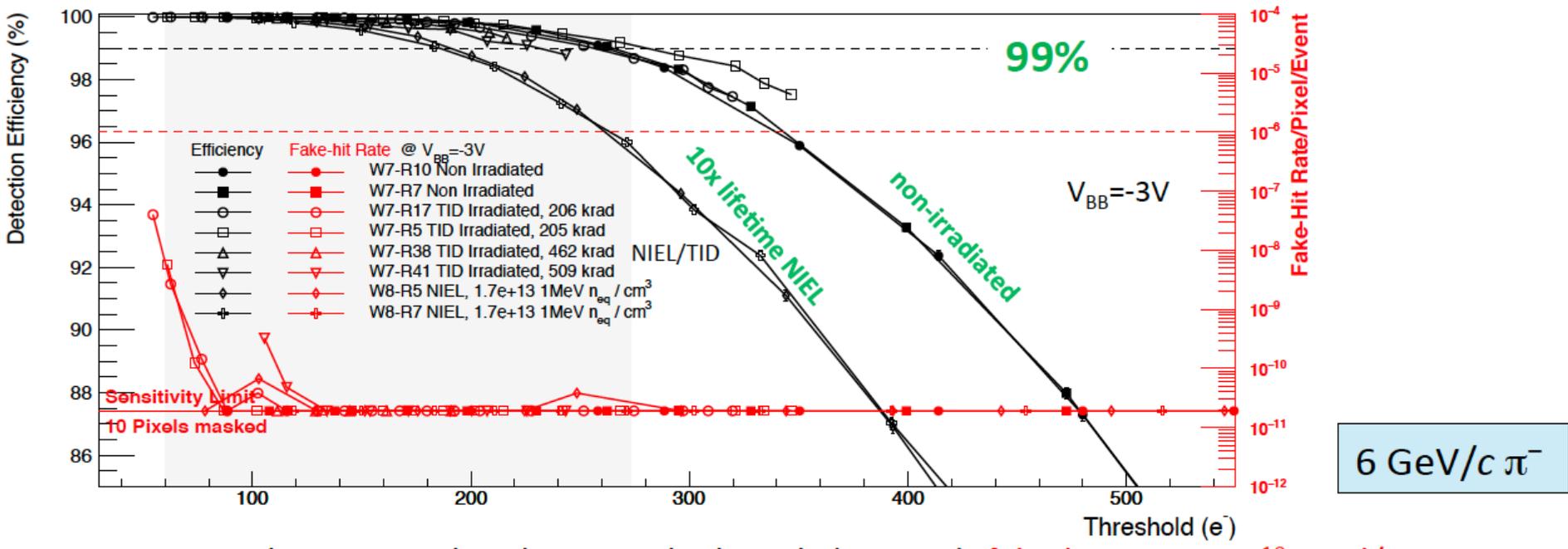
- Nb of charges on coll. diode depends on
 - Sensitive thickness
 - Potential distribution
- Conversion factor (capa)

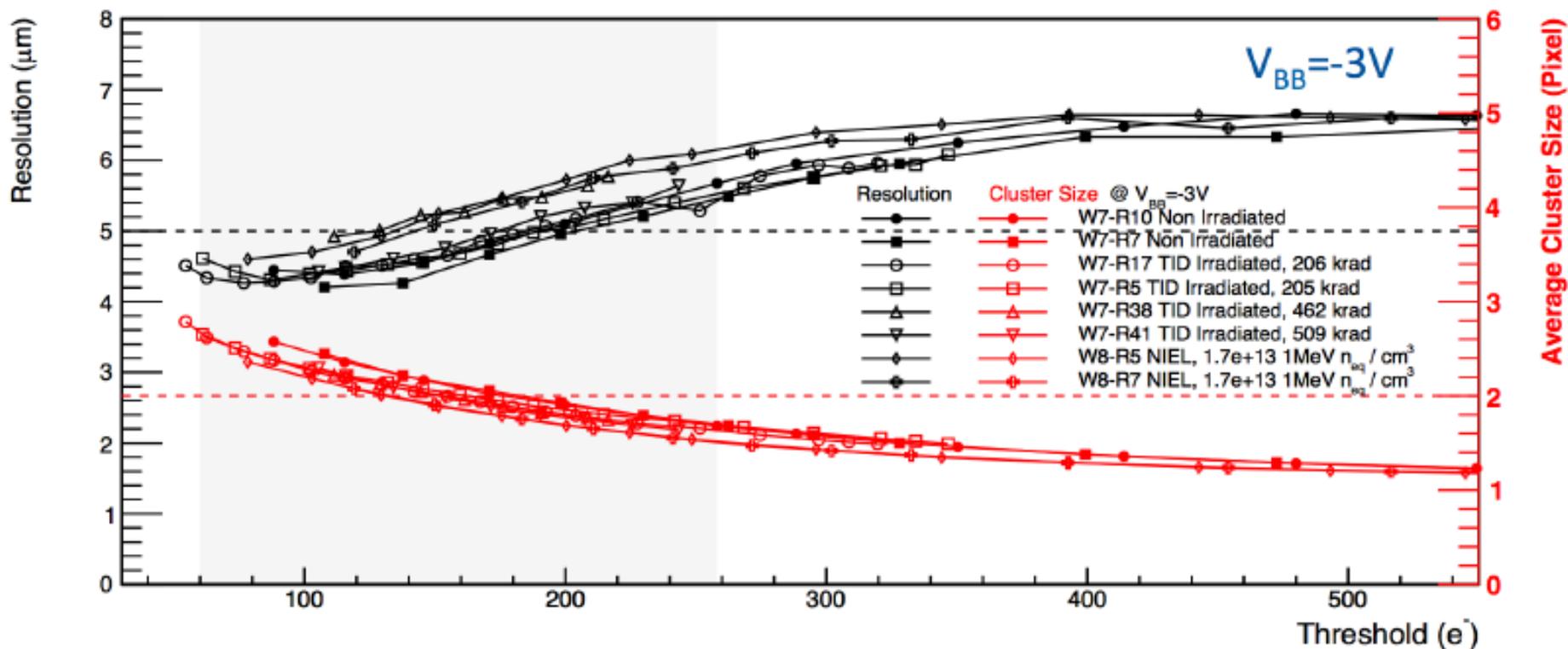
■ Noise

- Capacitance
- Leakage current

TID mitigation

ALICE - ALPIDE

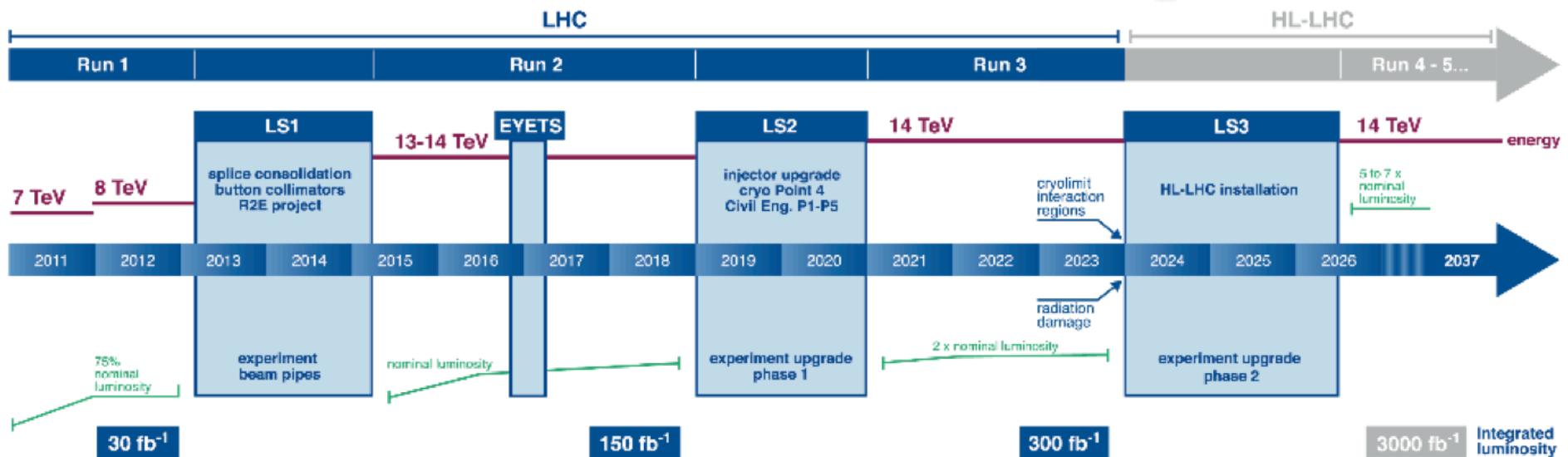




6 GeV π^-

LHC timeline

LHC / HL-LHC Plan



The PICSEL group in Starsbourg

General web site: iphc.cnrs.fr/picssel

■ Complementary expertise

- **Physicists**: 4 staffs, 1 post-doc, 3 PhD students
- **Micro-electronics** design: 11 staffs, 1 Post-docs, 2 PhD students
- (Micro-)electronic **test** : 5 staffs

■ Scientific production since 1998

- ~70 publications, ~50 proceedings, ~14 PhD defended
- ~50 **CMOS Pixel Sensors (CPS)** designed and characterized

■ Partners

- Academics:
 - CERN, , KEK (Japan), DESY (Hamburg), LNF (Frascati)
USA (Berkeley, Brookhaven), IHEP in China, many University groups
- CMOS foundries:
 - AMS (Austria), Tower-Jazz (Israel), TSMC (Taiwan), STM (France),
ESPROS (Switzerland)

Scientific drivers for the PICSEL group

EUDET 2006/2010

CERN, DESY, ...



STAR 2014 RHIC/BNL-USA



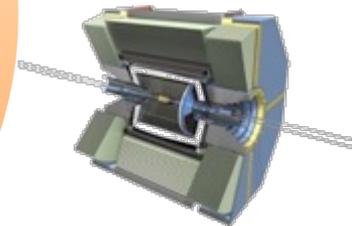
Tracking of charged particles

- Subatomic Physics
- Hadrontherapy

Imaging

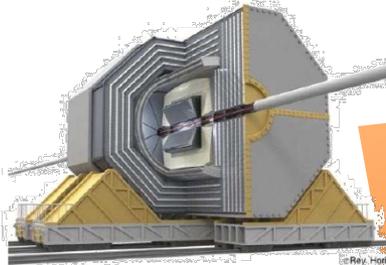
- Detection of β , low energy electrons
- Detection of X-rays
- Dosimetry
- Hybrid photo-detector
- bio-inspired vision

Belle II 2018 SuperKEKB-Japan



ILD ~2030

ILC-Japan

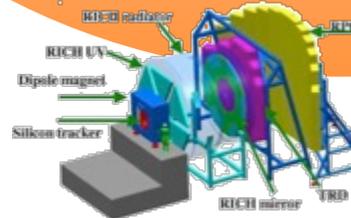


SOLEIL 2018

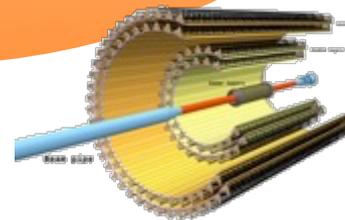
France



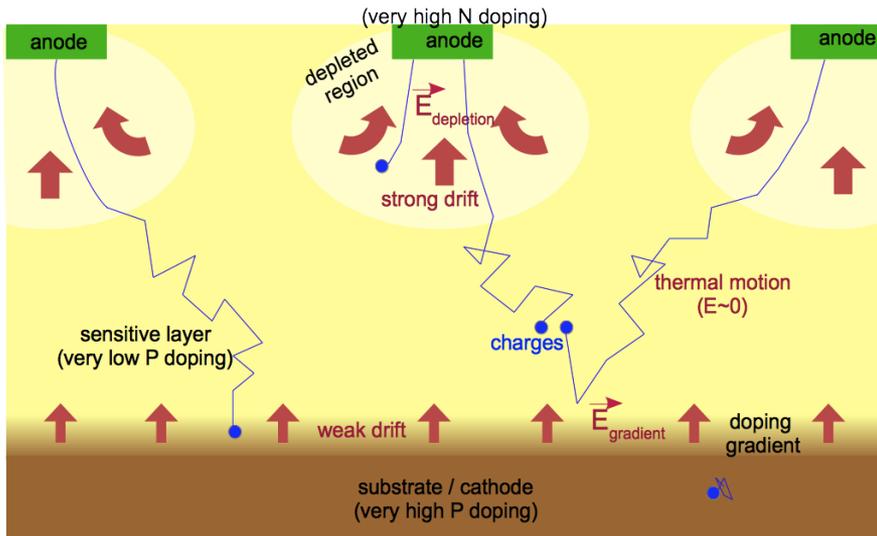
CBM >2019 FAIR/GSI-Germany



ALICE 2019 LHC/CERN



Standard “undepleted” MAPS



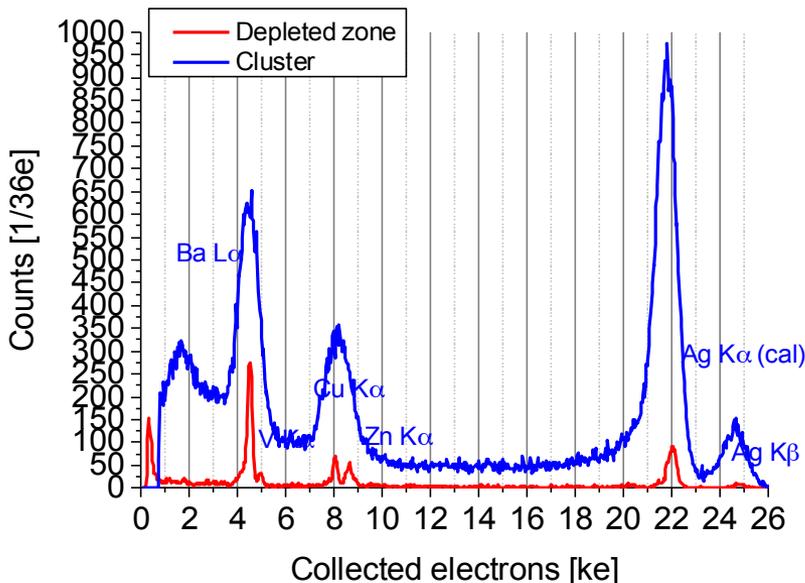
3 different E-field zones

- Zone extensions driven by
 - anode dimensions & spacing
 - anode/cathode potentials

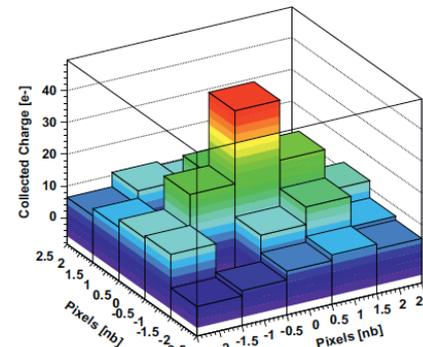
Depletion drives performances

- Deeper depletion →
 - Shrinks charge sharing / pixels
 - Increases signal/Noise per pixel
- Optimization required /
 - Detection sensitivity
 - Detection efficiency
 - Impact counting
 - Spatial resolution (or PSF)
 - Energy resolution

Fluorescence spectrum of the setup

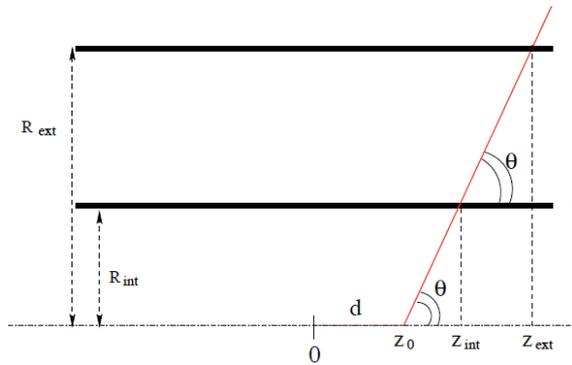


D.Doerhing, U.Goethe, Frankfurt

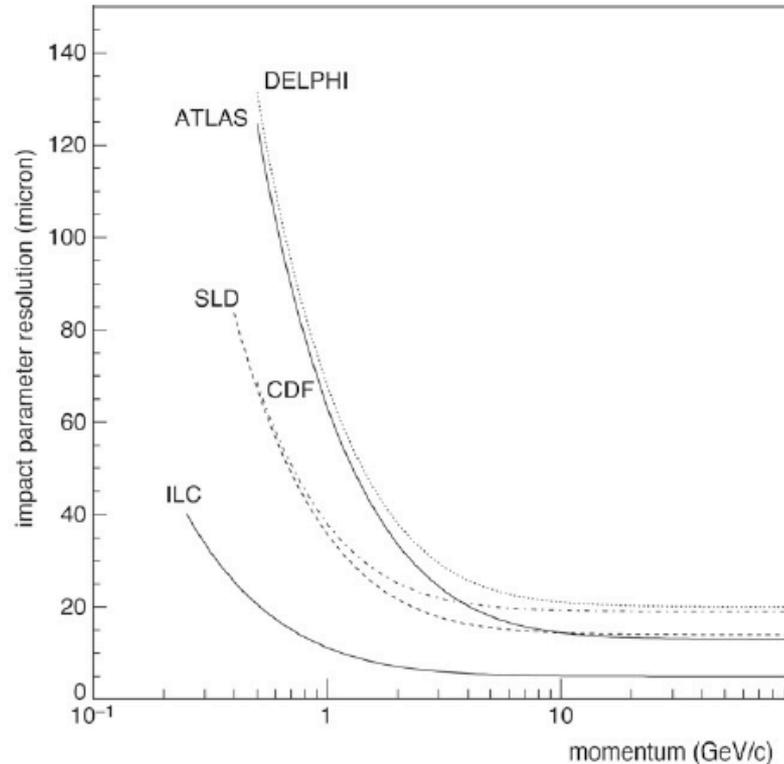


Charge cluster example (few keV electrons)

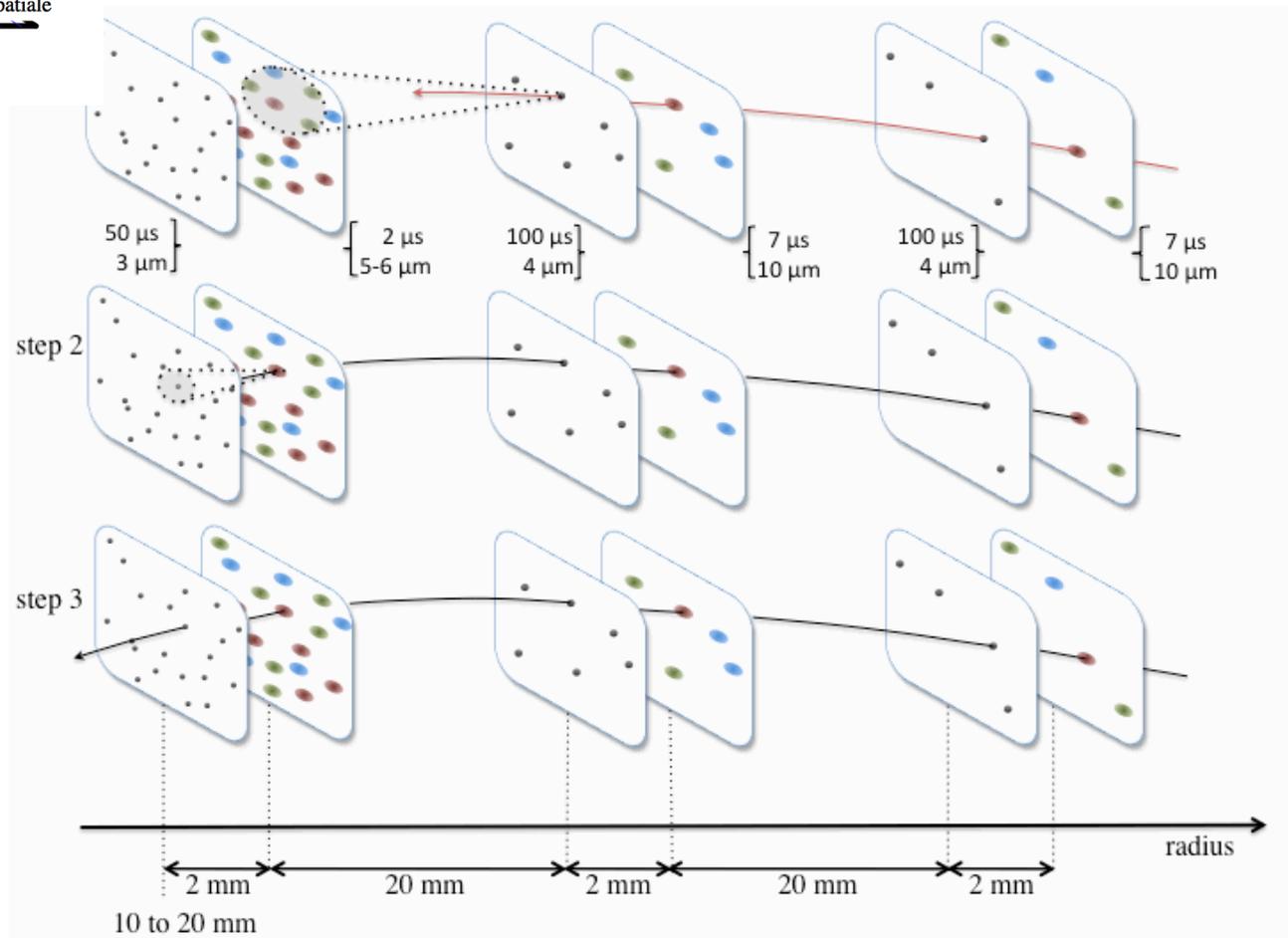
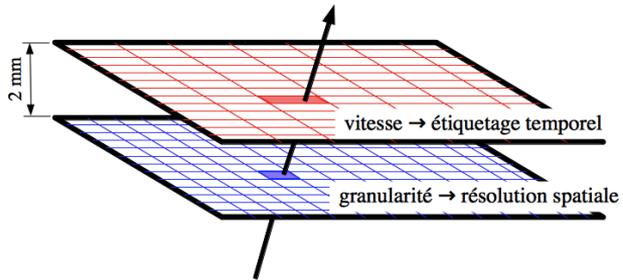
Impact parameter resolution



$$\sigma_{IP} \propto \frac{\sqrt{R_{ext}^2 \sigma_{int}^2 - R_{int}^2 \sigma_{ext}^2}}{R_{ext} - R_{int}} \oplus \frac{R_{int} \sigma_{\theta(ms)}}{p \sin^{3/2}(\theta)}$$



Tracking with doublets



MAPS are foldable !

B.Guenter et al., <https://doi.org/10.1364/OE.25.013010>

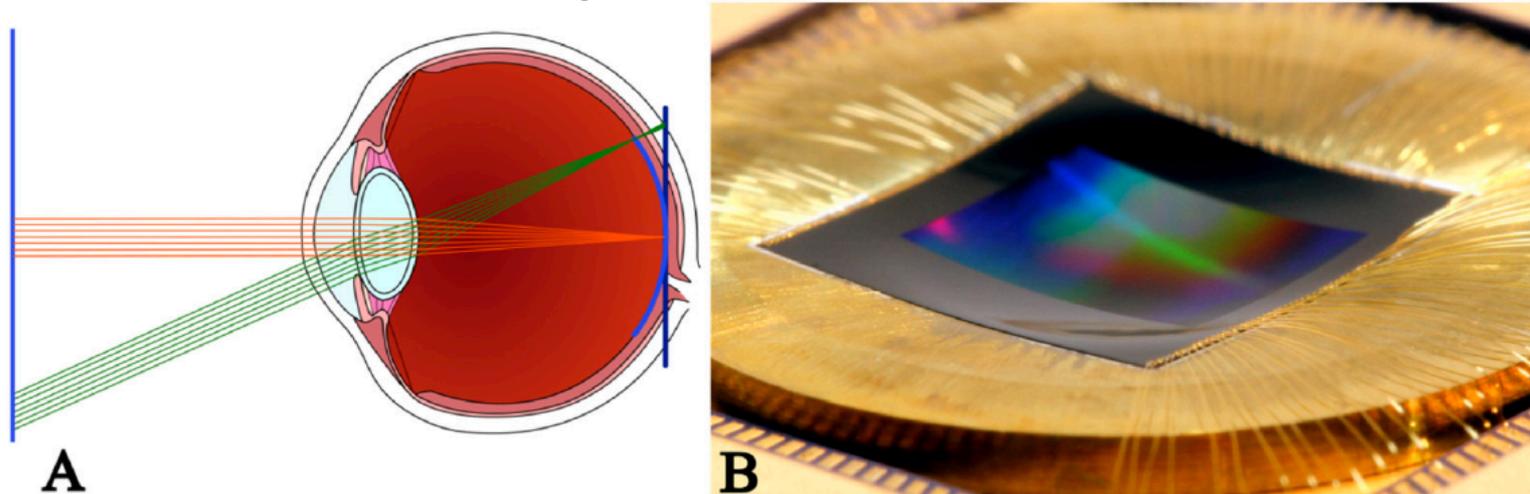


Fig. 1. A) The eye focuses onto photosensitive cells arranged along the curved focal surface inherent of a thick lens. Typical optical lenses require more elements and complexity to focus on flat focal planes and correct the aberrations these compensating elements introduce, losing performance compared to a curved focal plane. B) Functional, 18 megapixel (1/2.3" 7.6 mm x 7.7 mm die) BSI CMOS curved image sensor bonded to a precise 18.74 mm curved mold surface.

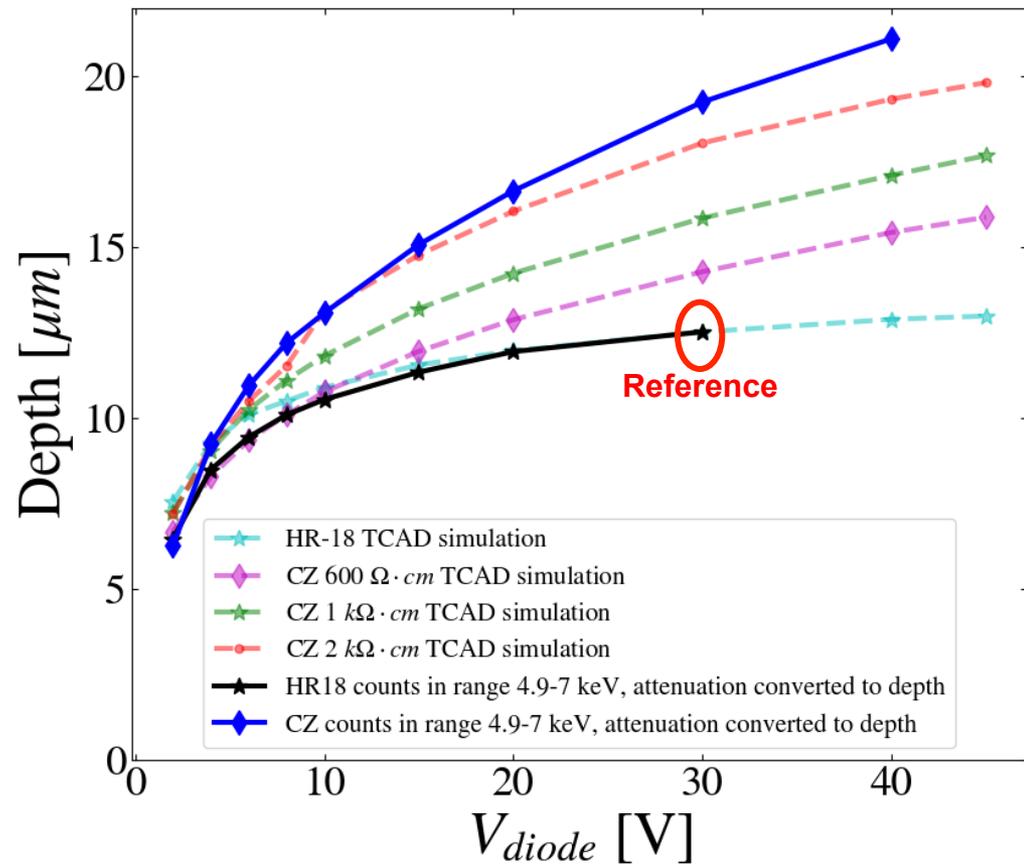
Own trial (IPHC, CERN)



Determination of the depletion depth

Using the ^{55}Fe calibration peaks – HR-18 vs. CZ

- Counts in range 4.9 keV – 7 keV
 - Depth determined from relative attenuation of HR-18 at 30 V
 - Maximum depleted depth 21 μm
 - Compared to TCAD simulations
 - Resistivity of 2 $\text{k}\Omega\cdot\text{cm}$

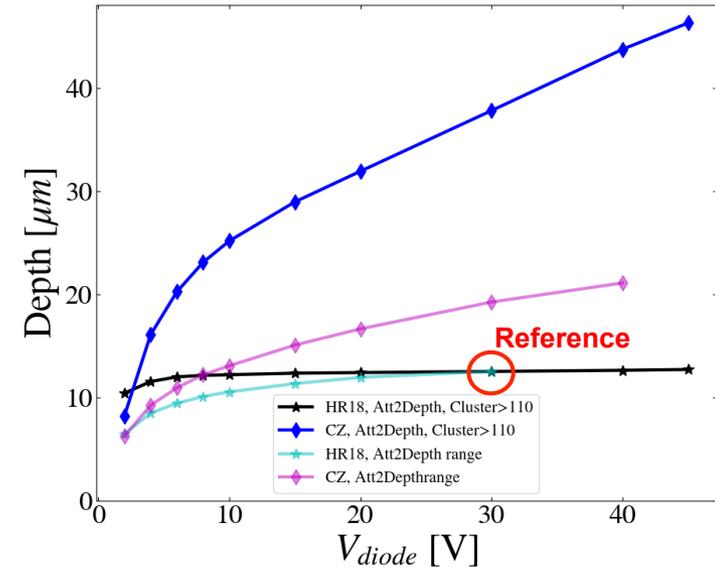


Determination of the depletion depth

Using the ^{55}Fe spectrum

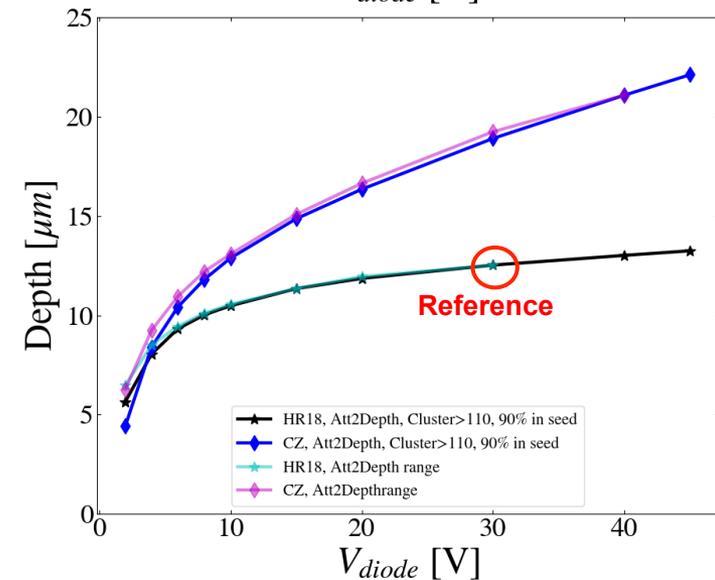
■ Total counts in spectrum after selection of hits in clusters > 110 ADCu

- Depth determined from relative attenuation to HR-18 at 30 V
 - HR18: Quick saturation around 12.5 μm
 - CZ: Depth increasing up to 46 μm (81 % attenuation for Mn-K α)
- ➔ Reaching the limit of sensitivity of ^{55}Fe



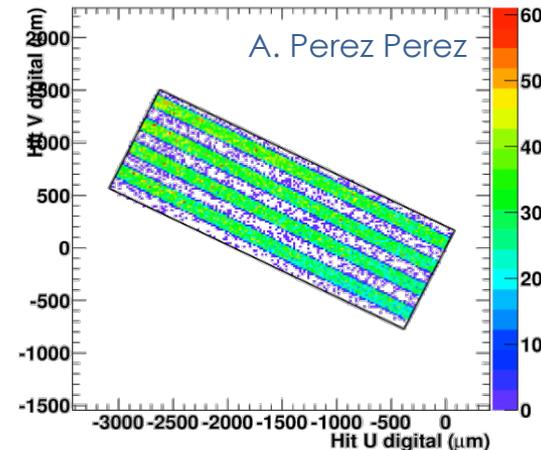
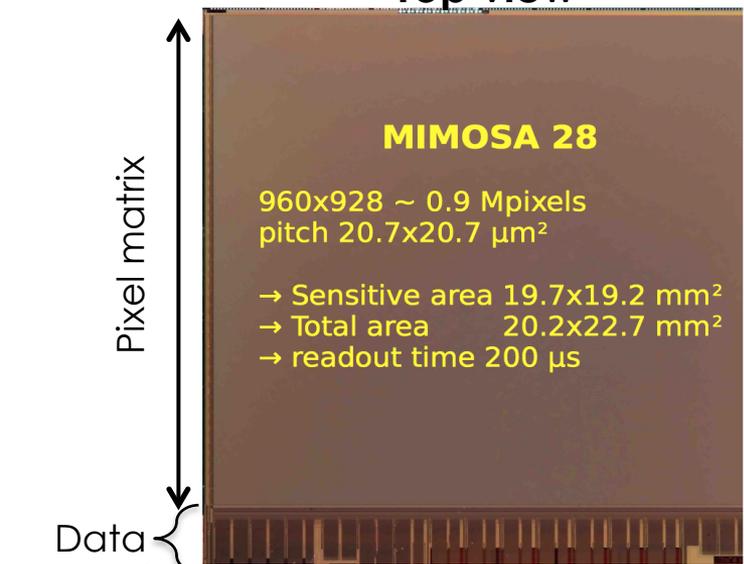
■ Total counts in spectrum after selection of hits in clusters > 110 ADCu and with 90 % of the charge on seed pixel

- Depth determined from relative attenuation to HR-18 at 30 V
 - Same behavior than 4.9-7 keV method
- ➔ HR18: depth reaching 13.25 μm
- ➔ CZ: depth reaching 22 μm



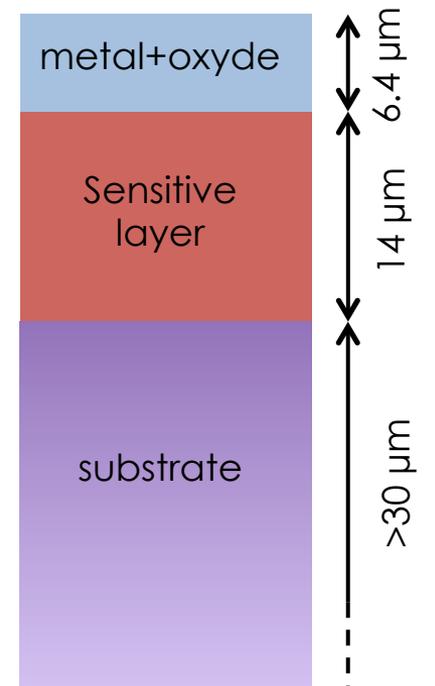
X-counting trial with previous tech.

Top view

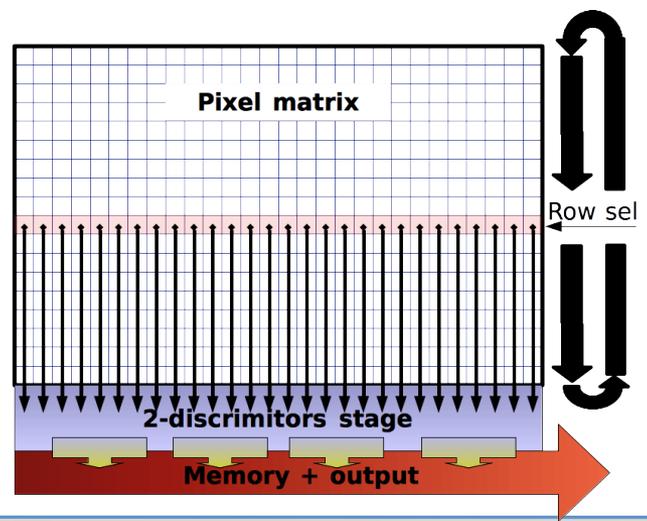


Test @ SOLEIL, $E_x = 6 \text{ keV}$
with similar sensor (pitch 18.4 μm)
→ Spatial resolution ~ 4 μm

Front (= illuminated side)



Side cut



Readout architecture
↓
single photon counting